RENESAS

RL78/I1E

RENESAS MCU

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- VDD= 2.4 to 5.5 V
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.03125 μs: @ 32 MHz operation with high-speed on-chip oscillator or PLL clock)^{Note} to ultra-low speed (1 μs: @ 1 MHz operation with highspeed on-chip oscillator or PLL clock)
- Multiply/divide/multiply & accumulate instructions are supported.
- Address space: 1 MB
- General-purpose registers: (8-bit register × 8) × 4 banks
- On-chip RAM: 8 KB
- Note For industrial applications (M; TA = -40 to $+125^{\circ}$ C): 0.04167 μ s @ 24 MHz operation with high-speed on-chip oscillator or PLL clock

Code flash memory

- Code flash memory: 32 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- Self-programming (with boot swap function/flash shield window function)

Data flash memory

- Data flash memory: 4 KB
- Back ground operation (BGO): Instructions can be executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: VDD = 2.4 to 5.5 V

High-speed on-chip oscillator

- Select from 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: ±2.0% (VDD = 2.4 to 5.5 V, TA = −40 to +105°C) ±3.0% (VDD = 2.4 to 5.5 V, TA = −40 to +125°C)

Operating ambient temperature

- TA = -40 to $+105^{\circ}$ C (G: Industrial applications)
- TA = -40 to $+125^{\circ}$ C (M: Industrial applications)

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 7 levels)

Data transfer controller (DTC)

- Transfer modes: Normal transfer mode, repeat transfer mode, block transfer mode
- Activation sources: Activated by interrupt sources.
- Chain transfer function

Event link controller (ELC)

Event signals of 16 types can be linked to the specified peripheral function.

Serial interfaces

- CSI: 2 channels
- UART: 2 channels (UART with LIN-bus supported: 1 channel)
- I²C/simplified I²C: 2 channels

Timer

- 16-bit timer: 8 channels (Timer Array Unit (TAU): 6 channels, timer RJ: 1 channel, timer RG: 1 channel)
- Interval timer: 1 channel
- Real-time clock: 1 channel (calendar for 99 years, alarm function, and clock correction function)
- Watchdog timer: 1 channel (operable with the dedicated low-speed on-chip oscillator)

Analog front-end (AFE) power supply

Sensor power supply (SBIAS) output: 0.5 V to 2.2 V

Datasheet

R01DS0274EJ0110 Rev. 1.10 Jun 30, 2016

- 24-bit $\Delta\Sigma$ A/D converter with programmable gain instrumentation amplifier
- 24-bit second-order $\Delta\Sigma$ A/D converter (AVDD = 2.7 to 5.5 V)
- SNDR: 85 dB (TYP.)
- Output data rate:
 488 sps to 15.625 ksps in normal mode
 61 sps to 1.953 ksps in low power mode
- Programmable gain instrumentation amplifier input: 3 or 4 channels
 - (differential input mode or single-ended input mode can be specified for each input channel)
- DAC for offset adjustment
- Variable gain: x1 to x64
- On-chip temperature sensor
- 10-bit A/D converter
- 8-bit/10-bit successive approximation A/D converter (AVDD = 2.7 to 5.5 V)
- Analog input: 8 or 10 channels, sensor power supply (SBIAS), and internal reference voltage
- Internal reference voltage (1.45 V)

Configurable amplifier

- Matrix configuration that consists of 3 operational amplifier channels and a configurable switch (AVDD = 2.7 to 5.5 V)
- Can be used as a 2- or 3-channel general operational amplifier
- Operational amplifier output: 3 channels
- General-purpose Analog I/O ports: 5 or 6 channels
- Offset voltage calibration

D/A converter

- 12-bit R-2R resistor ladder type D/A converter (AVDD = 2.7 to 5.5 V)
- Analog output: 1 channel (via configurable amplifier)

I/O port

- CMOS I/O: 10 to 14 (N-ch open drain I/O [withstanding voltage of VDD]: 6, CMOS I/O: 7 to 11, CMOS input: 3)
- Can be set to TTL input buffer and on-chip pull-up resistor
- Different potential interface: Can connect to a 2.5/3 V device
- On-chip clock output/buzzer output controller

Others

On-chip BCD (binary-coded decimal) correction circuit

O ROM, RA	M capacities
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Flash ROM	Data flash	RAM	RL78	3/I1E
Flash ROM	Data liasti	KAW	32 pins	36 pins
32 KB	4 KB	8 KB	R5F11CBC	R5F11CCC



1.2 Ordering Information

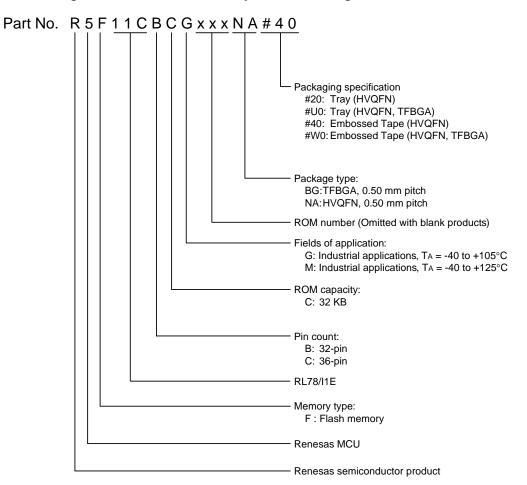


Figure 1 - 1 Part Number, Memory Size, and Package of RL78/I1E

Pin count	Package	Fields of Application _{Note}	Ordering Part Number
32 pins	32-pin plastic HVQFN (5 × 5 mm, 0.5 mm pitch)	G	R5F11CBCGNA#20 R5F11CBCGNA#40
		М	R5F11CBCMNA#U0 R5F11CBCMNA#W0
36 pins	36-pin plastic TFBGA (4 × 4 mm, 0.5 mm pitch)	G	R5F11CCCGBG#U0 R5F11CCCGBG#W0
		М	R5F11CCCMBG#U0 R5F11CCCMBG#W0

Note For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/I1E.

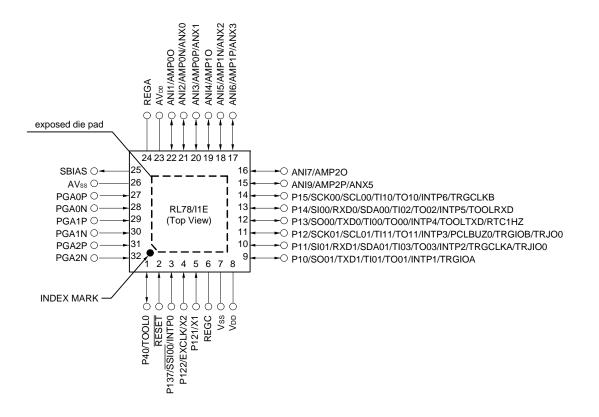
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

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1.3 Pin Configuration (Top View)

1.3.1 32-pin products

• 32-pin plastic HVQFN (5 × 5 mm, 0.5 mm pitch)



Caution 1. Connect the REGC pin to the Vss pin via a capacitor (0.47 to 1 $\mu\text{F}).$

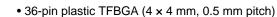
- Caution 2. Connect the REGA pin to the AVss pin via a capacitor (0.22 μ F).
- Caution 3. Make the AVss pin the same potential as the Vss pin.
- Caution 4. Make the AVDD pin the same potential as the VDD pin.
- Caution 5. Connect the SBIAS pin to the AVss pin via a capacitor (0.22 μ F).

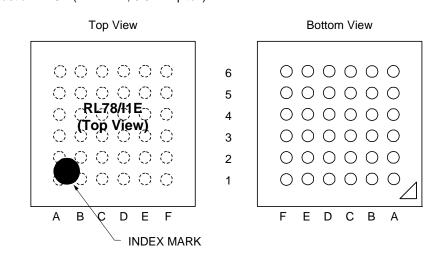
Remark 1. It is recommended to connect an exposed die pad to Vss.



1.3.2 36-pin products

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	А	В	С	D	Е	F	
6	PGA2P	PGA1N	PGA1P	PGA0P	PGA3P	AVss	6
5	PGA2N	P40/TOOL0	PGA0N	PGA3N	REGA	SBIAS	5
	RESET	P137/SSI00/ INTP0	P11/SI01/RXD1/ SDA01/TI03/	P12/SCK01/ SCL01/TI11/	ANIO	AVdd	
4			TO03/INTP2/ TRGCLKA/ TRJIO0	TO11/INTP3/ PCLBUZ0/ TRGIOB/TRJO0			4
3	P122/EXCLK/X2	P15/SCK00/ SCL00/T110/ TO10/INTP6/ TRGCLKB	P10/SO01/TXD1/ TI01/TO01/ INTP1/TRGIOA	ANI3/AMP0P/ ANX1	ANI2/AMPON/ ANX0	ANI1/AMP0O	3
2	P121/X1	REGC	P14/SI00/RXD0/ SDA00/TI02/ TO02/INTP5/ TOOLRXD	P41/ANI6/ AMP1P/ANX3	P42/ANI5/ AMP1N/ANX2	ANI4/AMP1O	2
1	Vdd	Vss	P13/SO00/TXD0/ TI00/TO00/INTP4/ TOOLTXD/ RTC1HZ	P16/INTP7/ANI9/ AMP2P/ANX5	P17/ANI8/ AMP2N/ANX4	ANI7/AMP2O	1
	А	В	С	D	E	F	1

Caution 1. Connect the REGC pin to the Vss pin via a capacitor (0.47 to 1 μ F).

Caution 2. Connect the REGA pin to the AVss pin via a capacitor (0.22 $\mu\text{F}).$

Caution 3. Make the AVss pin the same potential as the Vss pin.

Caution 4. Make the AVDD pin the same potential as the VDD pin.

Caution 5. Connect the SBIAS pin to the AVss pin via a capacitor (0.22 $\mu\text{F}).$

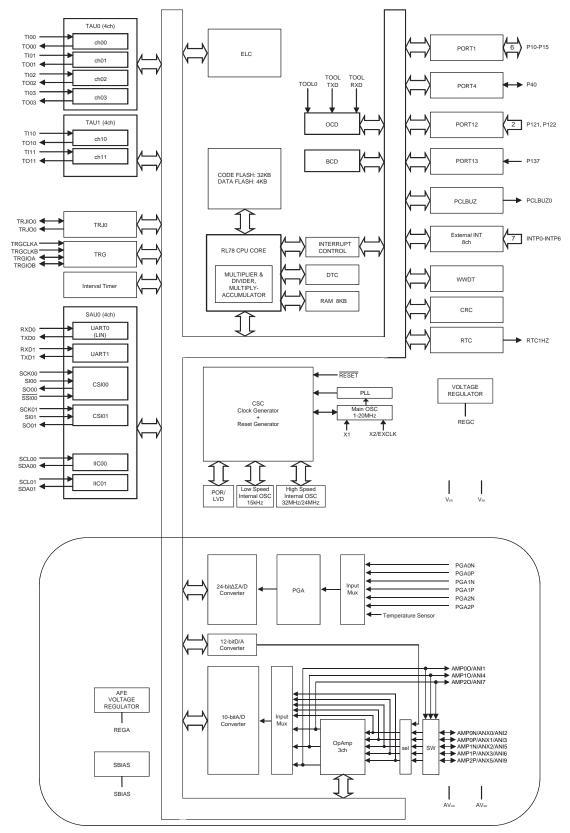
1.4 Pin Identification

ANI0 to ANI9:	Analog input	RESET:	Reset
AMP0P to AMP2P:	Operational amplifier	REGA:	Regulator capacitance for analog
	positive input	REGC:	Regulator capacitance
AMP0N to AMP2N:	Operational amplifier	RTC1HZ:	Real-time clock correction
	negative input	RxD0, RxD1:	Receive data
AMP0O to AMP2O:	Operational amplifier output	SBIAS:	Bias output for MEMS sensor
ANX0 to ANX5:	General-purpose analog	SCK00, SCK01:	Serial clock input/output
	ports for operational amplifier	SCL00, SCL01:	Serial clock output
AVDD:	Power supply for analog	SI00, SI01:	Serial data input
AVss:	Ground for analog	SO00, SO01:	Serial data output
EXCLK:	External clock input	TI00 to TI03, TI10, TI11:	Timer input
	(main system clock)	TO00 to TO03, TO10, TO11,	Timer output
INTP0 to INTP7:	External interrupt input	TRJO0:	
P10 to P17:	Port 1	TOOL0:	Data input/output for tools
P40 to P42:	Port 4	TOOLRxD, TOOLTxD:	Data input/output for external devices
P121, P122:	Port 12	TRGCLKA, TRGCLKB:	Timer external clock input
P137:	Port 13	TRGIOA, TRGIOB, TRJIO0:	Timer input/output
PCLBUZ0:	Programmable clock output/	TxD0, TxD1:	Transmit data
	buzzer output	Vdd:	Power supply
PGA0N to PGA3N:	PGA negative analog input	Vss:	Ground
PGA0P to PGA3P:	PGA positive analog input	X1, X2:	Crystal oscillator (main system clock)



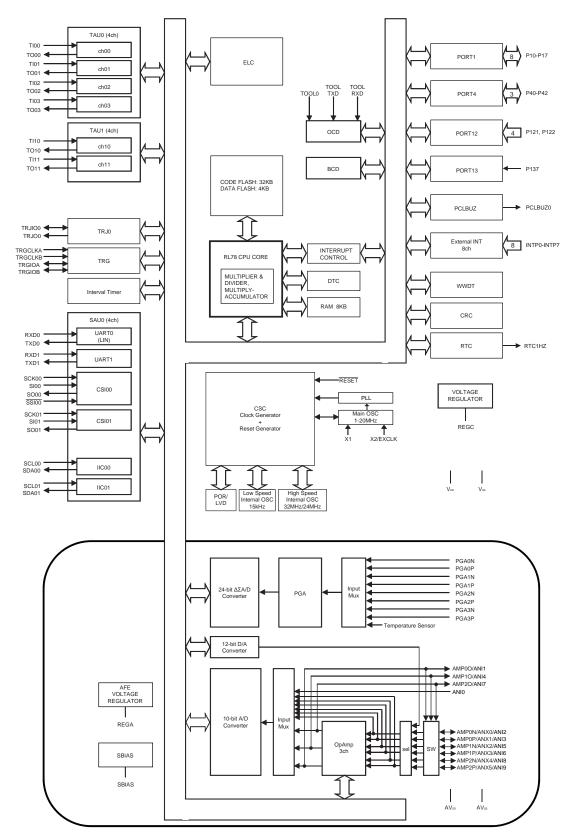
1.5 Block Diagram

1.5.1 32-pin products



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1.5.2 36-pin products



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1.6 Outline of Functions

[32-pin, 36-pin products]

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	Item	32-pin	36-pin			
		R5F11CBC	R5F11CCC			
Code flash mer	nory	32 KB				
Data flash merr	nory	4 KB				
RAM		8 KB				
Address space		1 MB				
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) 1 to 20 MHz: Vpd = 2.7 to 5.5 V, 1 to 16 MHz: Vpd = 2.4 to 2.7 V				
	High-speed on-chip oscillator clock (fiн)	1 to 32 MHz (V _{DD} = 2.7 to 5.5 V) ^{Note 1} 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V)				
	PLL clock (fPLL divided by 2, 4, or 8)	3 to 32 MHz (V _{DD} = 2.7 to 5.5 V) ^{Note 2} 3 to 16 MHz (V _{DD} = 2.4 to 5.5 V)				
General-purpos	se register	8 bits \times 32 registers (8 bits \times 8 registers \times 4 ban	ks)			
Minimum instru	ction execution time	0.03125 μ s (high-speed on-chip oscillator clock: fi μ = 32 MHz operation) ^{Note 3}				
		0.03125 μ s (PLL clock: fPLL = 64 MHz, fiH = 32 MHz operation) ^{Note 4}				
		0.05 µs (high-speed system clock: fмx = 20 MHz operation)				
Instruction set		 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits, 16 bits × 16 bits), division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) Multiplication and Accumulation (16 bits × 16 bits + 32 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 				
I/O port	Total	10	14			
	CMOS I/O	7	11			
	CMOS input	3	3			
Timer	16-bit timer	8 channels (TAU: 6 channels, Timer RJ: 1 chan	nel, Timer RG: 1 channel)			
	Watchdog timer	1 channel				
	Real-time clock (RTC)	1 channel				
	Interval timer	1 channel				
	Timer output	Timer outputs: 10 channels PWM outputs: 9 channels				
	RTC output	1				
Clock output/bu	izzer output	1				
		2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fMAIN = 20 MHz operation)				
8/10-bit A/D cor	nverter	8 channels	10 channels			
Serial interface		CSI: 2 channels/UART: 2 channels (UART supporting LIN-bus: 1 channel)/simplified I ² C: 2 channels				

Note 1. 1 to 24 MHz (VDD = 2.7 to 5.5 V) for M products (industrial applications, $T_A = -40$ to +125°C)

Note 2. 3 to 24 MHz (VDD = 2.7 to 5.5 V) for M products (industrial applications, $T_A = -40$ to $+125^{\circ}C$)

Note 3. 0.04167 μs (high-speed on-chip oscillator clock: fiH = 24 MHz operation) for M products (industrial applications, TA = -40 to +125°C)

Note 4. 0.04167 µs (PLL clock: fPLL = 64 MHz, fiH = 24 MHz operation) for M products (industrial applications, TA = -40 to +125°C



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			(2/2)		
	le .	32-pin	36-pin		
Item		R5F11CBC	R5F11CCC		
Data transfer controller (DTC)		22 sources			
Event link controller	r (ELC)	Event input: 16 Event trigger output: 7			
Vectored interrupt	Internal	23	23		
sources	External	7	8		
$\Delta\Sigma$ A/D converter	24-bit	3 channels	4 channels		
	AFE temperature sensor	1 channel			
Operational	3-pin	3 channels Note 1	3 channels		
amplifier	General-purpose port	5 channels	6 channels		
D/A converter	12-bit	1 channel			
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note 2 Internal reset by RAM parity error Internal reset by illegal-memory access			
Power-on-reset circ	cuit	 Power-on-reset: 1.56 ±0.03 V Power-down-reset: 1.55 ±0.03 V 			
Voltage detector		 At rise: 2.55 V to 4.64 V (7 steps) At fall: 2.61 V to 4.74 V (7 steps) 			
On-chip debug fund	ction	Provided			
Power supply voltage	ge	VDD = 2.4 to 5.5 V			
Operating ambient	temperature	T _A = -40 to +105°C (G: Industrial applications), T _A = -40 to +125°C (M: Industrial applications)			

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Note 1. When each of the 3 channels is in use as an independent amplifier, at least one channel must be in a voltage follower configuration.

Note 2. The illegal instruction is generated when instruction code FFH is executed. Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.



2. ELECTRICAL SPECIFICATIONS (G: TA = -40 to +105°C)

This chapter describes the electrical specifications for the products "G: Industrial applications (TA = -40 to +105°C)".

- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. The pins mounted depend on the product.
- Caution 3. Please contact Renesas Electronics sales office for derating of operation under TA = +85 to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.
- **Remark** The electrical characteristics of the products G: Industrial applications (TA = -40 to +105°C) are different from those of the products "M: Industrial applications". For details, refer to **2.1** to **2.10**.



2.1 **Absolute Maximum Ratings**

Absolute Maximum R	atings				(1/2)
Parameter	Symbol	Conc	litions	Ratings	Unit
Supply voltage	Vdd			-0.5 to +6.5	V
	AVdd	AVDD = VDD		-0.5 to +6.5	V
	AVss	AVss = Vss		-0.5 to +0.3	V
REGC pin input voltage	Viregc	REGC	REGC		V
REGA pin input voltage	Virega	REGA		-0.3 to +2.8 and -0.3 to AV _{DD} + 0.3 ^{Note 2}	V
Input voltage	VI1	P10 to P15, P40, P121, P122, P137, EXCLK, RESET		-0.3 to VDD +0.3 Note 3	V
Alternate-function pin	V12	P16, P17, P41, P42	Digital input voltage	-0.3 to VDD + 0.3 Note 3	V
input voltage		(36-pin products only)	Analog input voltage	-0.3 to AVDD + 0.3 Note 3	V
Analog input voltage	VIA	PGA0P to PGA3P, PG ANI0 to ANI9, ANX0 to	·	-0.3 to AVDD + 0.3 Note 3	V
Output voltage	V01	P10 to P15, P40		-0.3 to VDD + 0.3 Note 3	V
Alternate-function pin	Vo2	P16, P17, P41, P42	Digital output voltage	-0.3 to VDD + 0.3 Note 3	V
output voltage		(36-pin products only)	Analog output voltage	-0.3 to AVDD + 0.3 Note 3	V
Analog output voltage	Voa	SBIAS, AMP0O to AM	P2O, ANX0 to ANX5	-0.3 to AVDD + 0.3 Note 3	V

Absolute Maximum Ratings

Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Connect the REGA pin to AVss via a capacitor (0.22 µF). This value regulates the absolute maximum rating of the REGA pin. Do not use this pin with voltage applied to it.

- Note 3. Must be 6.5 V or lower.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Remark 2. Vss is used as the reference voltage.



Absolute Maximum Ratings

(2/2)Parameter Conditions Unit Symbol Ratings P10 to P17, P40 to P42 Output current, high IOH1 Per pin -40 mΑ Total of all pins P10 to P17, P41, P42 Note -100 mΑ Analog output current, Іона Per pin AMP0O to AMP2O -12 mΑ ANX0 to ANX5 -0.12 high mΑ Total of all pins AMP0O to AMP2O, ANX0 to ANX5 -18 mΑ Output current, low **I**OL1 Per pin P10 to P17, P40 to P42 40 mΑ Total of all pins 100 P10 to P17, P41, P42 Note mΑ Analog output current, low IOLA Per pin AMP0O to AMP2O 12 mΑ ANX0 to ANX5 0.12 mΑ Total of all pins AMP0O to AMP2O, ANX0 to ANX5 18 mΑ °C ΤA Operating ambient In normal operation mode -40 to +105 temperature In flash memory programming mode Storage temperature -65 to +150 °C Tstg

Note This indicates the total current value when P16, P17, P41, and P42 are used as digital input pins.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins. Remark 2. Vss is used as the reference voltage.



2.2 Oscillator Characteristics

2.2.1 X1 characteristics

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7~V \leq V\text{DD} \leq 5.5~V$	1.0		20.0	MHz
	crystal resonator	$2.4~\text{V} \leq \text{Vdd} < 2.7~\text{V}$	1.0		16.0	

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

2.2.2 On-chip oscillator characteristics

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency	fін	$2.7 V \le V \text{DD} \le 5.5 V$ $2.4 V \le V \text{DD} < 2.7 V$		1		32	MHz
Notes 1, 2				1		16	MHz
High-speed on-chip oscillator clock frequency accuracy		-40 to +105°C	$2.4~V \leq V \text{dd} \leq 5.5~V$	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 3 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.



2.2.3 PLL characteristics

ſ	TA = -40 to +105°C	2.4 V < AVDD	= VDD < 5.5 V.	AVss = Vss = 0 V)
•			- • • • • • • • • • • • • • • • • • • •	(100 - 100 - 0.1)

Parameter	Symbol	Conditions				TYP.	MAX.	Unit
PLL output frequencyNotes 1, 2,	fpll	fmx = 8 MHz	DSFRDIV = 0	DSCM = 0		48		MHz
3				DSCM = 1		64		MHz
			DSFRDIV = 1	DSCM = 0		24		MHz
				DSCM = 1		32		MHz
		fmx = 4 MHz	DSFRDIV = 0	DSCM = 0		24		MHz
				DSCM = 1		32		MHz
Lockup wait time			Time from when PLL output is enabled to when the phase is locked					μs
Interval wait time			Time from when the PLL stops operating to when the setting to start PLL operation is specified					μs
Setup wait time			Fime required from when the PLL input clock stabilizes and the PLL setting is determined to when the PLL is activated					μs

Note 1. When using a PLL, input a clock of 4 MHz or 8 MHz to the PLL.

Note 2. Be sure to specify one of these settings when using a PLL.

Note 3. When using the PLL output as the CPU clock, f_{IH} is divided by 2, 4, or 8 according to the setting of the RDIV1 and RDIV0 bits.



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2.3 DC Characteristics

2.3.1 Pin characteristics

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Item	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P10 to P17 and P40 to P42 Note 2	-40°C < TA ≤ +85°C			-10.0 Note 3	mA
			85°C < TA ≤ 105°C			-3.0 Note 3	mA
		Total of P10 to P17, P41, and P42 Note 2	$4.0 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$ -40°C < Ta \le +85°C			-80.0	mA
		(When duty \leq 70% ^{Note 4})	$\begin{array}{l} 4.0 \ V \leq VDD \leq 5.5 \ V \\ 85^{\circ}C < TA \leq 105^{\circ}C \end{array}$			-30.0	mA
			$2.7~\text{V} \leq \text{VDD} < 4.0~\text{V}$			-19.0	mA
			$2.4~\text{V} \leq \text{VDD} < 2.7~\text{V}$			-10.0	mA
Output current, low Note 1	IOL1	Per pin for P10 to P17 and P40 to P42 Note 2	-40°C < TA ≤ +85°C			20.0 Note 3	mA
			85°C < TA ≤ 105°C			8.5 Note 3	mA
		Total of P10 to P17, P41, and P42 Note 2	$4.0 V \le VDD \le 5.5 V$ -40°C < TA \le +85°C			80.0	mA
		(When duty \leq 70% ^{Note 4})	$\begin{array}{l} 4.0 \ V \leq VDD \leq 5.5 \ V \\ 85^{\circ}C < TA \leq 105^{\circ}C \end{array}$			40.0	mA
			$2.7~\text{V} \leq \text{Vdd} < 4.0~\text{V}$			35.0	mA
			$2.4~\text{V} \leq \text{VDD} < 2.7~\text{V}$			20.0	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin.

Note 2. This indicates the total current value when P16, P17, P41, and P42 are used as digital I/O ports. When using these pins as analog function (AFE) pins, refer to 2.1 Absolute Maximum Ratings.

Note 3. Do not exceed the total current value.

Note 4. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$

Example: n = 80% when IOH = -10.0 mA

Total output current of pins = (-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P10 to P15 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



	1		. ,	i	i		(2/3
Item	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P10 to P17 and P40 to P42	Normal input buffer	0.8 Vdd		Vdd	V
	VIH2	P11, P12, P14,	TTL input buffer, 4.0 V \leq VDD \leq 5.5 V	nput buffer 0.8 VDD VDD at buffer, $4.0 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$ 2.2 VDD at buffer, $3.3 \text{ V} \le \text{VDD} < 4.0 \text{ V}$ 2.0 VDD at buffer, $2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}$ 1.5 VDD at buffer, $2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}$ 1.5 VDD at buffer, $2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}$ 0.8 VDD VDD nput buffer 0 0.2 VDD at buffer, $4.0 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$ 0 0.8 at buffer, $3.3 \text{ V} \le \text{VDD} < 4.0 \text{ V}$ 0 0.5 at buffer, $2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}$ 0 0.32 at buffer, $2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}$ 0 0.32 at buffer, $2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}$ 0 0.32 buffer, $2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}$ 0 0.32 buffer, $2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}$ 0 0.2 VDD /DD $\leq 5.5 \text{ V},$ VDD < 1.5 0.2 VDD /DD $\leq 5.5 \text{ V},$ VDD < 0.7 0.7 f $A \le 105^{\circ}$ C, IOH1 = -1.5 mA VDD < 0.5 0.7 /DD $\leq 5.5 \text{ V},$ ID $= 1.5 \text{ mA}$ <t< td=""><td>V</td></t<>	V		
		P15	TTL input buffer, 3.3 V \leq VDD < 4.0 V	2.0	VDD	Vdd	V
			TTL input buffer, 2.4 V \leq VDD < 3.3 V	1.5		Vdd	V
	Vінз	P121, P122, P13	7, EXCLK, RESET	0.8 Vdd		Vdd	V
Input voltage, low	VIL1	P10 to P17 and P40 to P42	Normal input buffer	0		0.2 Vdd	V
	VIL2	P11, P12, P14,	TTL input buffer, 4.0 V \leq VDD \leq 5.5 V	0		0.8	V
		P15	TTL input buffer, 3.3 V \leq VDD < 4.0 V	0		0.5	V
			TTL input buffer, 2.4 V \leq VDD < 3.3 V	0		0.32	V
	VIL3 P121, P122, P137, EXCLK, RESET 0 0.2 V	0.2 Vdd	V				
Output voltage, high	VOH1	P10 to P17 and P40 to P42	4.0 V \leq Vdd \leq 5.5 V, TA = -40 to +85°C, Ioh1 = -10.0 mA	Vdd - 1.5			V
			4.0 V \leq Vdd \leq 5.5 V, 85°C < TA \leq 105°C, IoH1 = -3.0 mA	Vdd - 0.7			V
			$2.7~V \leq V\text{DD} \leq 5.5~V\text{, IOH1}$ = -2.0 mA	Vdd - 0.6			V
			$2.4~V \leq V\text{DD} \leq 5.5~V\text{, IOH1}$ = -1.5 mA	Vdd - 0.5			V
Output voltage, low	VOL1	P10 to P17 and P40 to P42	$4.0 \text{ V} \le \text{Vdd} \le 5.5 \text{ V},$ TA = -40 to +85°C, lol1 = 20.0 mA			1.3	V
			4.0 V \leq Vdd \leq 5.5 V, 85°C < TA \leq 105°C, Iol1 = 8.5 mA			0.7	V
			$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}, \text{ Iol1} = 3.0 \text{ mA}$			0.6	V
			$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}, \text{ Iol1} = 1.5 \text{ mA}$			0.4	V
			$2.4~V \leq V\text{DD} \leq 5.5~V,~\text{IOL1} = 0.6~\text{mA}$			0.4	V

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

(2/3)

Caution The maximum VIH value on P10 to P15 is VDD, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Item	Symbol	Conc	ditions		MIN.	TYP.	MAX.	Unit
Input leakage	ILIH1	P10 to P17, and P40 to P42	VI = VDD				1	μΑ
current, high	ILIH2	P137, RESET	VI = VDD				1	μA
	Іцнз	P121, P122 (X1, X2, EXCLK)	VI = VDD	In input port mode or when using external clock input			1	μΑ
				When a resonator is connected			10	μA
Input leakage	ILIL1	P10 to P17, and P40 to P42	VI = VSS	VI = VSS			-1	μΑ
current, low	ILIL2	P137, RESET	VI = VSS				-1	μA
	ILIL3	P121, P122 (X1, X2, EXCLK)	VI = VSS	In input port mode or when using external clock input			-1	μA
				When a resonator is connected			-10	μA
On-chip pull-up resistance	Ru	P10 to P15, P40	VI = Vss, ii	n input port mode	10	20	100	kΩ

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(3/3)

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



RL78/I1E

2.3.2 Supply current characteristics

		°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)							(1/2
Parameter	Symbol		Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	fhoco = 32 MHz, fmain = 32 MHz Note 3	Basic	Vdd = 5.0 V		2.1		m/
current Note 1		mode ^{Note 2}		operation	VDD = 3.0 V		2.1		1
NOTE 1			fHOCO = 32 MHz, fMAIN = 32 MHz Note 3	Normal	VDD = 5.0 V		4.8	8.7	m/
				operation	VDD = 3.0 V		4.8	8.7	
			fHOCO = 24 MHz, fMAIN = 24 MHz Note 3	Normal	VDD = 5.0 V		3.8	6.7	
				operation	VDD = 3.0 V		3.8	6.7	
			fHOCO = 16 MHz, fMAIN = 16 MHz Note 3	Normal	Vdd = 5.0 V		2.8	4.9	
				operation	VDD = 3.0 V		2.8	4.9	
			fmx = 20 MHz, fmain = 20 MHz ^{Note 4} ,	Normal	Square wave input		3.3	5.7	m
		VDD = 5.0 V	operation	Resonator connection		3.5	5.8		
		fmx = 20 MHz, fmain = 20 MHz ^{Note 4} ,	Normal	Square wave input		3.3	5.7]	
	V _{DD} = 3.0 V operation	operation	Resonator connection		3.5	5.8			
			fmx = 10 MHz, fmain = 10 MHz Note 4,	Normal	Square wave input		2.0	3.4	
			Vdd = 5.0 V	operation	Resonator connection		2.1	3.5	
			fmx = 10 MHz, fmain = 10 MHz ^{Note 4} ,	Normal	Square wave input		2.0	3.4	
			Vdd = 3.0 V	operation	Resonator connection		2.1	3.5	
			fmx = 8 MHz, fmain = 32 MHz Note 5,	Normal	Square wave input		5.2	9.2	m
			VDD = 5.0 V	operation	Resonator connection		5.3	9.3	
			fmx = 8 MHz, fmain = 32 MHz Note 5,	Normal	Square wave input		5.2	9.2	
			Vdd = 3.0 V	operation	Resonator connection		5.3	9.3	
			fmx = 8 MHz, fmain = 24 MHz ^{Note 5} ,	Normal	Square wave input		5.1	9.1	
			Vdd = 5.0 V	operation	Resonator connection		5.2	9.2	1
			f _{MX} = 8 MHz, f _{MAIN} = 24 MHz ^{Note 5} ,	Normal	Square wave input		5.1	9.1	1
			VDD = 3.0 V	operation	Resonator connection		5.2	9.2	1

- Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the RTC, interval timer, watchdog timer, LVD circuit, AFE, I/O ports, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. The relationship between the operation voltage range and the CPU operating frequency is as below. $2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$ @ 1 MHz to 32 MHz $2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$ @ 1 MHz to 16 MHz
- Note 3. When the high-speed system clock is stopped
- Note 4. When the high-speed on-chip oscillator and the PLL are stopped
- Note 5. When the high-speed on-chip oscillator is stopped and the PLL is operating

High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency) Remark 1. fmx:

- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency
- Remark 3. fMAIN: Main system clock frequency
- Remark 4. The temperature condition for the TYP. value is TA = 25°C



	i	i	$\sqrt{D} = \sqrt{D} \sum 3.3 \sqrt{4}, \sqrt{3} 3 = \sqrt{3} 3 = \sqrt{4}$			T) (D		(2/2
Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Supply current	IDD2	HALT mode	fhoco = 32 MHz, fmain = 32 MHz Note 4	VDD = 5.0 V		0.54	3.67	mA
Note 1	Note 2	Note 3		VDD = 3.0 V		0.54	3.67	
			fhoco = 24 MHz, fmain = 24 MHz Note 4	VDD = 5.0 V		0.44	2.85	
				VDD = 3.0 V		0.44	2.85	
			fhoco = 16 MHz, fmain = 16 MHz Note 4	VDD = 5.0 V		0.40	2.08	
				VDD = 3.0 V		0.40	2.08	
			f_{MX} = 20 MHz, f_{MAIN} = 20 MHz $^{Note \; 5}, \; V_{DD}$ = 5.0 V	Square wave input		0.28	2.45	mA
				Resonator connection		0.49	2.57	
		fmx = 20 MHz, fmain = 20 MHz Note 5, Vdd = 3.0 V	Square wave input		0.28	2.45		
				Resonator connection		0.49	2.57	
		fmx = 10 MHz, fmain = 10 MHz Note 5, Vdd = 5.0 V	Square wave input		0.19	1.28		
				Resonator connection		0.30	1.36	
			fmx = 10 MHz, fmain = 10 MHz Note 5, Vdd = 3.0 V	Square wave input		0.19	1.28	
				Resonator connection		0.30	1.36	
			fmx = 8 MHz, fmain = 32 MHz ^{Note 6} , Vdd = 5.0 V	Square wave input		0.91	4.17	mA
				Resonator connection		1.01	4.27	
			fmx = 8 MHz, fmain = 32 MHz Note 6, VDD = 3.0 V	Square wave input		0.91	4.17	
				Resonator connection		1.01	4.27	
			fmx = 8 MHz, fmain = 24 MHz ^{Note 6} , V _{DD} = 5.0 V	Square wave input		0.76	3.27	
				Resonator connection		0.86	3.37	
			fmx = 8 MHz, fmain = 24 MHz Note 6, VDD = 3.0 V	Square wave input		0.76	3.27	
				Resonator connection		0.86	3.37	
IDD3 STO Note 7	STOP mode	TA = -40°C	•		0.38	1.14	μΑ	
		TA = +25°C			0.50	1.14		
			$T_A = +50^{\circ}C$			0.66	4.52	
		TA = +70°C			1.04	7.98		
			TA = +85°C			2.92	16.0	
			T _A = +105°C			11.0	100.0	1

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{AVDD} = \text{VDD} \le 5.5 \text{ V}, \text{AVss} = \text{Vss} = 0 \text{ V})$

(2/2)

- Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the RTC, interval timer, watchdog timer, LVD circuit, AFE, I/O ports, and on-chip pull-up/pull-down resistors and the current flowing during writing to the data flash.
- **Note 2.** During HALT instruction execution from flash memory
- **Note 3.** The relationship between the operation voltage range and the CPU operating frequency is as below.
 - 2.7 V \leq VDD \leq 5.5 V @ 1 MHz to 32 MHz
 - 2.4 V \leq VDD \leq 5.5 V @ 1 MHz to 16 MHz
- Note 4. When the high-speed system clock is stopped
- Note 5. When the high-speed on-chip oscillator and the PLL are stopped
- Note 6. When high-speed on-chip oscillator is stopped and the PLL is operating
- Note 7. The MAX. value includes the leakage current in STOP mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency
- Remark 3. fMAIN: Main system clock frequency
- **Remark 4.** The temperature condition for the TYP. value is $T_A = 25^{\circ}C$, except the operation in STOP mode.



• Peripheral functions

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol	Condit	ions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I _{FIL} Note 1				0.20		μΑ
RTC operating current	IRTC Notes 1, 2, 3	fмx = 4 MHz, RTCCL = 00H (fм	x = 4 MHz, RTCCL = 00H (f _{MX} /122)				μΑ
Interval timer operating current	I _{IT} Notes 1, 2, 4	$f_{MX} = 4$ MHz, RTCCL = 00H (fm	MX = 4 MHz, RTCCL = 00H (f _{MX} /122)				μA
Watchdog timer operating current	I _{WDT} Notes 1, 5, 6	fı∟ = 15 kHz			0.22		μA
LVD operating current	I _{LVD} Notes 1, 7				0.08		μΑ
Self-programming operating current	_{FSP} Notes 1, 8				2.50	12.20	mA
BGO operating current	IBGO Notes 1, 9				2.50	12.20	mA
SNOOZE operating	I _{SNOZ} Note 1	A/D converter operation ^{Notes}	The mode is performed		0.50	1.10	mA
current		10,	During A/D conversion, AV _{DD} = V _{DD} = 3.0 V		1.20	2.04	
		CSI/UART operation	•		0.70	1.54	
		DTC operation			3.10		

Note 1. Current flowing to VDD

Note 2. When the high-speed on-chip oscillator is stopped

Note 3. Current flowing only to the real-time clock (RTC). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock is operating in operation mode or HALT mode.

- **Note 4.** Current flowing only to the interval timer. The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the interval timer is operating in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, also add IFIL.
- Note 5. When the high-speed on-chip oscillator and high-speed system clock are stopped.
- **Note 6.** Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).
- The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is operating.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is operating.
- Note 8. Current flowing during self-programming
- Note 9. Current flowing during writing to the data flash
- **Note 10.** The current flowing into the AV_{DD} is included.

Remark 1. fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

- Remark 2. fiL: Low-speed on-chip oscillator clock frequency
- **Remark 3.** The temperature condition for the TYP. value is $TA = 25^{\circ}C$



AFE functions

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(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)
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Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
24-bit $\Delta\Sigma$ A/D converter operating current	Idsad	Normal mode Notes 1, 2 Circuits that operate: ABGR, REGA, SBIAS, VREFAMP, PGA, 24-bit $\Delta\Sigma$ A/D converter, and digital filter Differential input mode OSR = 256 SBIAS Iout = 0 mA		0.94	1.46	mA
		Low power mode Notes 1, 2 Circuits that operate: ABGR, REGA, SBIAS, VREFAMP, PGA, 24-bit $\Delta\Sigma$ A/D converter, and digital filter Differential input mode OSR = 256 SBIAS lour = 0 mA		0.60	0.91	mA
10-bit A/D converter operating current	IADC	During conversion at the highest speed Notes 1, 2 $AV_{DD} = 5.0 V$		1.30	1.70	mA
Configurable amplifier operating current	IAMP	Normal mode Notes 1, 2 Circuits that operate: ABGR and configurable amplifier IL = 0 mA Per channel		0.13	0.24	mA
		High-speed mode Notes 1, 2 Circuits that operate: ABGR and configurable amplifier IL = 0 mA Per channel		0.30	0.45	mA
12-bit D/A converter operating current	Idac	When AV _{DD} is selected as the reference voltage Notes 1, 2 Circuits that operate: ABGR and internal reference voltage (VREFDA)		0.61	0.97	mA

Note 1. Current flowing to AVDD

Note 2. Current flowing only to the circuits that operate shown in the Conditions column.



2.4 AC Characteristics

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle	Тсү	Main system clock (fMAIN) operation	$2.7~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$	0.03125		1	μS
(minimum instruction			$2.4~\text{V} \leq \text{VDD} < 2.7~\text{V}$	0.0625		1	μS
execution time)		In the self-programming mode	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	0.03125		1	μs
			$2.4~\text{V} \leq \text{VDD} < 2.7~\text{V}$	0.0625		1	μs
External system clock	fex	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$		1.0		20.0	MHz
frequency		$2.4 \text{ V} \leq \text{Vdd} < 2.7 \text{ V}$		1.0		16.0	MHz
External system clock	texн,	$2.7~V \leq V \text{DD} \leq 5.5~V$		24			ns
input high-level width, low-level width	texl	$2.4~\text{V} \leq \text{Vdd} < 2.7~\text{V}$		30			ns
TI00 to TI03, TI10, TI11 input high-level width, low-level width	ttiH, tti∟			1/fмск + 10			ns
Timer RJ input cycle	fc	TRJIO0	$2.7~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$	100			ns
			$2.4~\text{V} \leq \text{VDD} < 2.7~\text{V}$	300			ns
Timer RJ input high-	tтjiн,	TRJIO0	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	40			ns
level width, low-level width	t⊤ji∟		$2.4~\text{V} \leq \text{Vdd} < 2.7~\text{V}$	120			ns
Timer RG input high- level width, low-level width	ttgih, ttgi∟	TRGIOA, TRGIOB		2.5/fclk			ns
TO00 to TO03,	fтo		$4.0~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			16	MHz
TO10, TO11,			$2.7~V \leq V \text{DD} \leq 4.0~V$			8	MHz
TRJIO0, TRJO0, TRGIOA, TRGIOB output frequency			$2.4 \text{ V} \leq \text{VDD} < 2.7 \text{ V}$			4	MHz
PCLBUZ0 output	fpcl		$4.0~V \leq V \text{DD} \leq 5.5~V$			16	MHz
frequency			$2.7~V \leq V_{DD} \leq 4.0~V$			8	MHz
			$2.4~\text{V} \leq \text{VDD} < 2.7~\text{V}$			4	MHz
Interrupt input high- level width, low-level width	tinth, tintl	INTP1 to INTP7		1			μS
RESET low-level width	trsl			10			μS

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

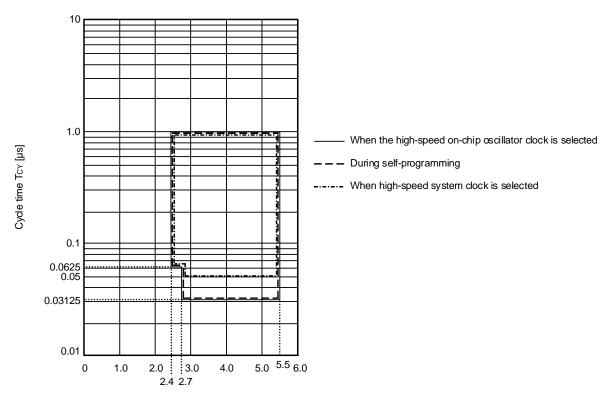
Remark fMCK: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))



TCY vs VDD

Minimum Instruction Execution Time During Main System Clock Operation

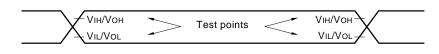


Supply voltage VDD [V]

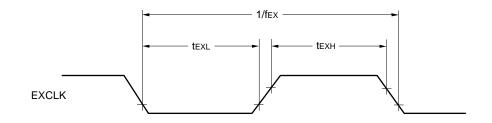
R01DS0274EJ0110 Rev. 1.10 Jun 30, 2016



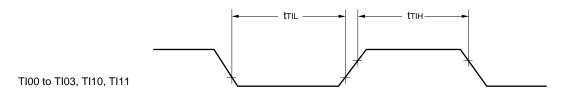
AC Timing Test Points

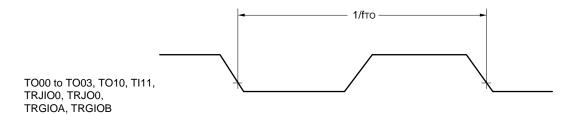


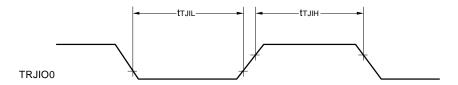
External System Clock Timing



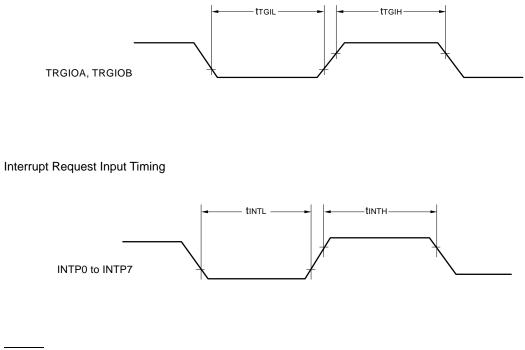
TI/TO Timing



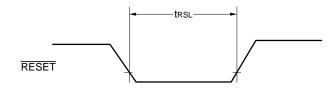








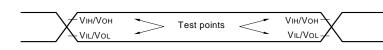
RESET Input Timing





2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	ed main) Mode	Unit
			MIN.	MAX.	
Transfer rate Note 1				fмск/12	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 2$		2.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

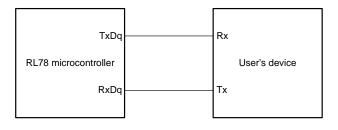
Note 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLk) are:

32 MHz (2.7 V \leq VDD \leq 5.5 V)

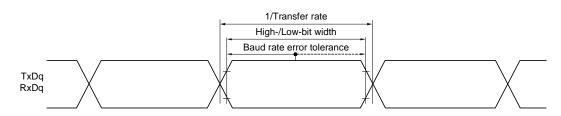
16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0, 1), g: PIM or POM number (g = 1)

Remark 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) (TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Ol Conditions		, s ,	HS (high-speed main) mode	
					MAX.	
SCKp cycle time	tkCY1	$t_{KCY1} \geq 4/f_{CLK}$	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	250		ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	500		ns
SCKp high-/low-level width	tĸнı, tĸ∟ı	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		tксү1/2 - 24		ns
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		tксү1/2 - 36		ns
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		tксү1/2 - 76		ns
SIp setup time (to SCKp [↑]) Note 1	tsik1	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$		66		ns
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		66		ns
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		113		ns
SIp hold time (from SCKp↑) Note 1	tksi1			38		ns
Delay time from SCKp↓ to SOp output Note 2	tkso1	C = 30 pF Note	e 3		50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM number (g = 1)

Remark 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))



(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions		HS (high-spee	Unit	
				MIN.	MAX.	
SCKp cycle time Note 1	tKCY2	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	20 MHz < fмск	16/fмск		ns
			fмск ≤ 20 MHz	12/fмск		ns
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	16 MHz < fмск	16/fмск		ns
			fмск ≤ 16 MHz	12/fмск		ns
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		12/fмск and 1000		ns
SCKp high-/low-level width	tkH2, tkL2	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$		tксү2/2 - 14		ns
		$2.7 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$		tксү2/2 - 16		ns
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		tксү2/2 - 36		ns
SIp setup time (to SCKp↑) Note 2	tsik2	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		1/fмск + 40		ns
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 2	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output	tkso2	C = 30 pF Note 4	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		2/fмск + 66	ns
Note 3			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		2/fмск + 113	ns
SSI00 setup time	tssik	DAPmn = 0	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	240		ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	400		ns
		DAPmn = 1	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1/fмск + 240		ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	1/fмск + 400		ns
SSI00 hold time	tĸssi	DAPmn = 0	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1/fмск + 240		ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	1/fмск + 400		ns
		DAPmn = 1	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	240		ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	400		ns

Note 1. The maximum transfer rate in the SNOOZE mode is 1 Mbps.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

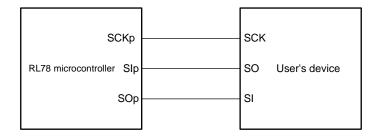
Caution Select the normal input buffer for the SIp and SCKp pins and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM number (g = 1)

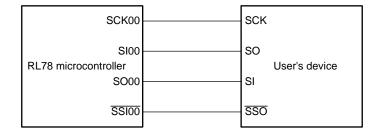
Remark 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))



CSI mode connection diagram (during communication at same potential)

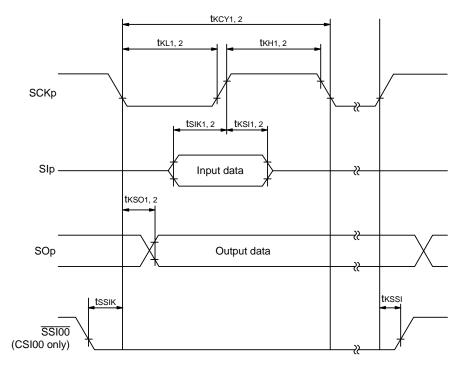


CSI mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))



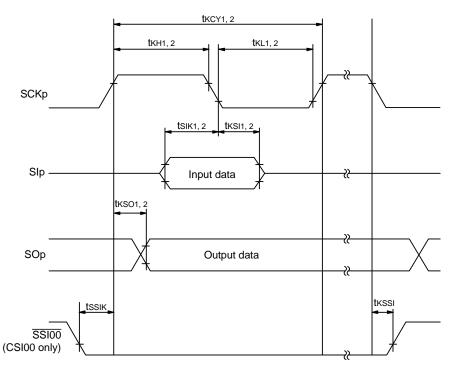
Remark 1. p: CSI number (p = 00, 01) Remark 2. m: Unit number, n: Channel number (mn = 00, 01)





CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01) Remark 2. m: Unit number, n: Channel number (mn = 00, 01)

RENESAS

(4) During communication at same potential (simplified I²C mode)

Parameter	Symbol	Conditions	HS (high-spee	Unit	
			MIN.	MAX.	
SCLr clock frequency	fsc∟	$\label{eq:VDD} \begin{array}{l} 2.7 \mbox{ V} \leq \mbox{V}_{\mbox{DD}} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 2.7 \mbox{ k}\Omega \end{array}$		400 Note 1	kHz
		$\label{eq:VDD} \begin{split} 2.4 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 3 \ \text{k}\Omega \end{split}$		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ C_{\text{b}} = 50 \ \text{pF}, \ R_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	1200		ns
		$\label{eq:VDD} \begin{split} 2.4 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 3 \ \text{k}\Omega \end{split}$	4600		ns
Hold time when SCLr = "H"	tніgн	$\label{eq:VDD} \begin{array}{l} 2.7 \mbox{ V} \leq V_{DD} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 2.7 \mbox{ k}\Omega \end{array}$	1200		ns
		$\label{eq:VDD} \begin{split} 2.4 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 3 \ \text{k}\Omega \end{split}$	4600		ns
Data setup time (reception)	tsu: dat	$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ C_{\text{b}} = 50 \ \text{pF}, \ R_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	1/fмск + 220 Note 2		ns
		$\label{eq:VDD} \begin{array}{l} 2.4 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 3 \ \text{k}\Omega \end{array}$	1/fмск + 580 Note 2		ns
Data hold time (transmission)	thd: dat	$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ C_{\text{b}} = 50 \ \text{pF}, \ R_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	0	770	ns
		$\label{eq:VDD} \begin{split} 2.4 \ V \leq V_{\text{DD}} \leq 5.5 \ \text{V}, \\ C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 3 \ \text{k}\Omega \end{split}$	0	1420	ns

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{AV}\text{DD} = \text{V}\text{DD} \le 5.5 \text{ V}, \text{AV}\text{ss} = \text{V}\text{ss} = 0 \text{ V})$

Note 1. The value must also be equal to or less than fmck/4.

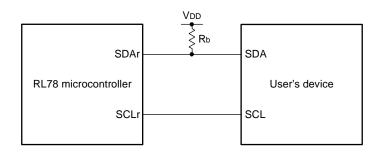
Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

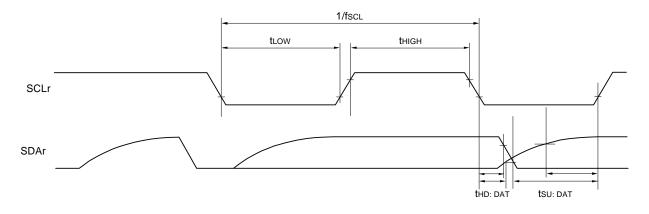
(Remarks are listed on the next page.)



Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remark 1. Rb [Ω]: Communication line (SDAr) pull-up resistance, Cb [F]: Communication line (SDAr, SCLr) load capacitance

Remark 2. r: IIC number (r = 00, 01), g: PIM number (g = 1), h: POM number (h = 1)

Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0, 1), mn = 00, 01)



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(1/2)

Parameter Symbol Symbol Transfer rate Rec		Conditions		HS (high-speed main) mode		Unit		
				MIN.	MAX.			
	Reception	4.0	$V \leq V_{\text{DD}} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq V_b \leq 4.0 \text{ V}$		fмск/12 Note 1	bps		
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 2$		2.6	Mbps	
			2.7	$V \leq V_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \leq V_b \leq 2.7 \text{ V}$		fмск/12 Note 1	bps	
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 2$		2.6	Mbps			
		2.4	$V \leq V_{\text{DD}} < 3.3$ V, 1.6 V $\leq V_{\text{b}} \leq 2.0$ V		fмск/12 Note 1	bps		
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 2$		2.6	Mbps			

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLk) are:

32 MHz (2.7 V \leq VDD \leq 5.5 V) 16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remark 1. Vb [V]: Communication line voltage

Remark 2. q: UART number (q = 0, 1), g: PIM or POM number (g = 1)

Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01)



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(2/2)

	,		,,			(
Parameter Symbol		Conditions	HS (high-speed main) mode		Unit	
				MIN.	MAX.	
Transfer rate		Transmission	$4.0~\text{V} \leq \text{V}_\text{DD} \leq 5.5~\text{V},~2.7~\text{V} \leq \text{V}_b \leq 4.0~\text{V}$		Note 1	bps
			Theoretical value of the maximum transfer rate $C_{\rm b}$ = 50 pF, $R_{\rm b}$ = 1.4 k Ω , $V_{\rm b}$ = 2.7 V		2.6 Note 2	Mbps
			$ \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array} $		Note 3	bps
		Theoretical value of the maximum transfer rate $C_{\rm b}$ = 50 pF, $R_{\rm b}$ = 2.7 k Ω , $V_{\rm b}$ = 2.3 V		1.2 Note 4	Mbps	
		$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \end{array}$		Note 5	bps	
		Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$		0.43 Note 6	Mbps	

Note 1. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq VDD \leq 5.5 V and 2.7 V \leq Vb \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
[bps]
Baud rate error (theoretical value) =
$$\frac{\frac{1}{Transfer rate \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{Transfer rate}) \times Number of transferred bits}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 2.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate = -

rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$

1

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 4.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



Note 5. The smaller maximum transfer rate derived by using fMcK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq VDD < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times 100 [\%]}$$

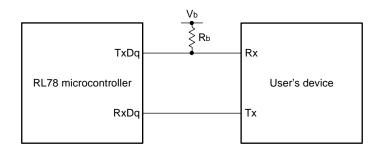
* This value is the theoretical value of the relative difference between the transmission and reception sides.

- Note 6.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

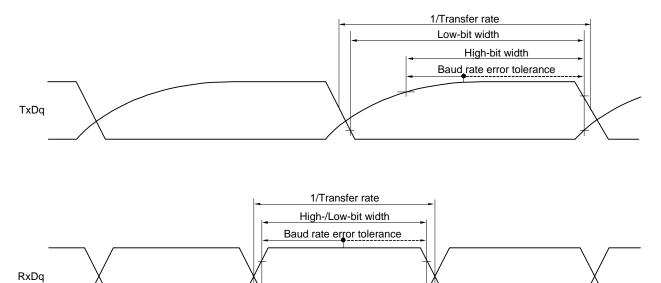
(Remarks are listed on the next page.)



UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Remark 1. Rb $[\Omega]$: Communication line (TxDq) pull-up resistance,

Cb [F]: Communication line (TxDq) load capacitance, Vb [V]: Communication line voltage

Remark 2. q: UART number (q = 0, 1), g: PIM or POM number (g = 1)

Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)
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(1/3)

Parameter	Symbol	Conditions		HS (high-speed	l main) mode	Unit
				MIN.	MAX.	
SCKp cycle time	tксү1	tксү1 ≥ 4/f с∟к		600		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1000		ns	
			$\label{eq:VD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	2300		ns
SCKp high-level width	tкнı	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \\ \hline 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		tксү1/2 - 150		ns
				tксү1/2 - 340		ns
2.4 V ≤ 1 1.6 V ≤ 1		$\begin{array}{l} 2.4 \ V \leq V_{DD} < \\ 1.6 \ V \leq V_b \leq 2 \\ C_b = 30 \ pF, \ R_b \end{array}$.0 V,	tксү1/2 - 916		ns
SCKp low-level width	tκ∟ı	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$		tĸcy1/2 - 24		ns
2.3		$2.3~V \leq V_b \leq 2$	$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$			ns
	$\label{eq:2.4} \begin{array}{ c c c } \hline 2.4 \ V \leq V_{DD} < 3. \\ \hline 1.6 \ V \leq V_b \leq 2.0 \\ \hline C_b = 30 \ pF, \ R_b = \end{array}$.0 V,	tксү1/2 - 100		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

/T. A0.1- A0500		
$(1A = -40 \text{ to } +105^{\circ}\text{C})$, 2.4 V \leq AVDD = VDD \leq :	5.5 V, AVss = Vss = 0 V)

(2/3)

Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) ^{Note}	tsik1		162		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ p\text{F}, \ R_b = 2.7 \ k\Omega \end{array}$	354		ns
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 30 \; p\text{F}, \; R_b = 5.5 \; k\Omega \end{split}$	958		ns
SIp hold time (from SCKp↑) ^{Note}	tksii		38		ns
		$\label{eq:VDD} \begin{split} & 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ & 2.3 \ V \leq V_b \leq 2.7 \ V, \\ & C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	38		ns
		$\label{eq:VDD} \begin{split} & 2.4 \ V \leq V_{DD} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V, \\ & C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	38		ns
Delay time from SCKp↓ to SOp output ^{Note}	tkso1			200	ns
		$\label{eq:VDD} \begin{split} & 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ & 2.3 \ V \leq V_b \leq 2.7 \ V, \\ & C_b = 30 \ p\text{F}, \ R_b = 2.7 \ k\Omega \end{split}$		390	ns
		$\label{eq:VDD} \begin{split} & 2.4 \ V \leq V_{DD} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V, \\ & C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

/T. A0.1- A0500		
$(1A = -40 \text{ to } +105^{\circ}\text{C})$, 2.4 V \leq AVDD = VDD \leq :	5.5 V, AVss = Vss = 0 V)

(3/3)

Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note}	tsikı		88		ns
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	88		ns
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	220		ns
SIp hold time (from SCKp↓) ^{Note}	tksii		38		ns
		$\label{eq:VD} \begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	38		ns
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	38		ns
Delay time from SCKp↑ to SOp output ^{Note}	tkso1			50	ns
		$\label{eq:VD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$		50	ns
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$		50	ns

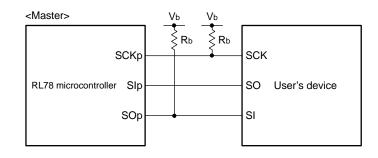
Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)



CSI mode connection diagram (during communication at different potential

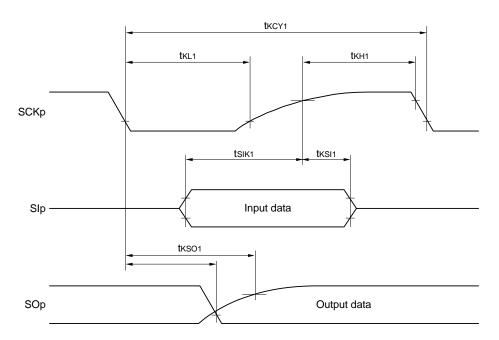


Remark 1. Rb [Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb [F]: Communication line (SCKp, SOp) load capacitance, Vb [V]: Communication line voltage

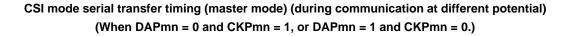
Remark 2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1) **Remark 3.** fMCK: Serial array unit operation clock frequency

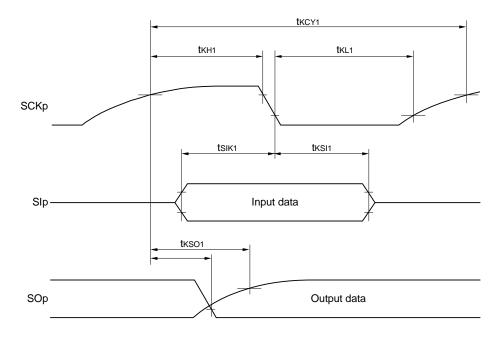
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))





CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

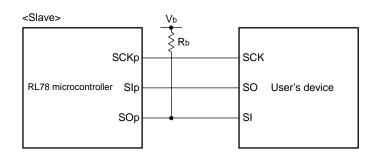
Parameter	Symbol	Conditions		HS (high-spe	Unit	
				MIN.	MAX.	
SCKp cycle time Note 1	t ксү2	$4.0~V \leq V_{\text{DD}} \leq 5.5~V,$	24 MHz < fмск	28/fмск		ns
		$2.7~V \leq V_b \leq 4.0~V$	$20 \text{ MHz} < f_{\text{MCK}} \leq 24 \text{ MHz}$	24/f мск		ns
			$8 \text{ MHz} < f_{\text{MCK}} \le 20 \text{ MHz}$	20/fмск		ns
			$4 \; MHz < f_{\text{MCK}} \leq 8 \; MHz$	16/f мск		ns
			fмск ≤ 4 MHz	12/f мск		ns
		$2.7~V \leq V_{\text{DD}} < 4.0~V,$	24 MHz < fмск	40/f мск		ns
		$2.3~V \leq V_b \leq 2.7~V$	$20 \text{ MHz} < f_{\text{MCK}} \leq 24 \text{ MHz}$	32/f мск		ns
			$16 \text{ MHz} < f_{\text{MCK}} \le 20 \text{ MHz}$	28/fмск		ns
			$8 \text{ MHz} < f_{\text{MCK}} \leq 16 \text{ MHz}$	24/f мск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \leq 8 \text{ MHz}$	16/f мск		ns
			fмск \leq 4 MHz	12/f мск		ns
		$2.4~V \leq V_{\text{DD}} < 3.3~V,$	24 MHz < fмск	96/f мск		ns
		$1.6~V \leq V_b \leq 2.0~V$	$20 \text{ MHz} < f_{\text{MCK}} \leq 24 \text{ MHz}$	72/f мск		ns
			$16 \text{ MHz} < f_{\text{MCK}} \leq 20 \text{ MHz}$	64/fмск		ns
			$8 \text{ MHz} < f_{\text{MCK}} \leq 16 \text{ MHz}$	52/f мск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \leq 8 \text{ MHz}$	32/f мск		ns
			fмск \leq 4 MHz	20/f мск		ns
SCKp high-/low-level	tкн2, tк∟2	$4.0~\text{V} \leq \text{V}_\text{DD} \leq 5.5~\text{V}, 2$	$2.7~V \leq V_b \leq 4.0~V$	tксү2/2 - 24		ns
width		$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} < 4.0~\textrm{V},2$	$2.3~V \leq V_b \leq 2.7~V$	tксү2/2 - 36		ns
		$2.4~\text{V} \leq \text{V}_\text{DD} < 3.3~\text{V},~1$	$1.6~V \leq V_b \leq 2.0~V$	tксү2/2 - 100		ns
SIp setup time	tsik2	$4.0~\text{V} \leq \text{V}_\text{DD} \leq 5.5~\text{V}, 2$	$2.7~V \leq V_b \leq 4.0~V$	1/fмск + 40		ns
(to SCKp↑) Note 2		$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} < 4.0~\textrm{V},2$	$2.3~V \leq V_b \leq 2.7~V$	1/fмск + 40		ns
		$2.4~\text{V} \leq \text{V}_\text{DD} < 3.3~\text{V},~1$	$1.6~V \leq V_b \leq 2.0~V$	1/fмск + 60		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output	tĸso2	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2$ $C_{\text{b}} = 30 \text{ pF}, \text{R}_{\text{b}} = 1.4 \text{ J}$			2/fмск + 240	ns
Note 3			$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$		2/fмск + 428	ns
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1$ $C_{\text{b}} = 30 \text{ pF}, \text{Rb} = 5.5$	$1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V},$		2/fмск + 1146	ns

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

(Notes, Cautions, and Remarks are listed on the next page.)

- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp and SCKp pins, and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)

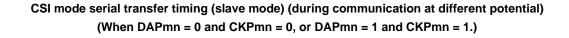


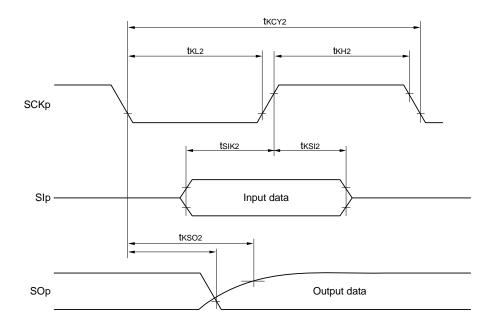
- **Remark 1.** Rb [Ω]: Communication line (SOp) pull-up resistance, Cb [F]: Communication line (SOp) load capacitance, Vb [V]: Communication line voltage
- Remark 2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)
- Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

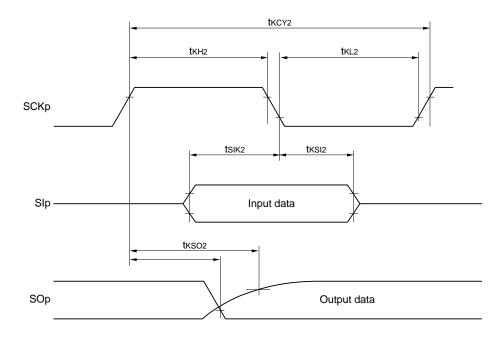
Remark 4. Communication at different potential cannot be performed during clocked serial communication with the slave select function.







CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)
 Remark 2. Communication at different potential cannot be performed during clocked serial communication with the slave select function.

RENESAS

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(1/2)

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
SCLr clock frequency	fsc∟			400 Note 1	kHz
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 50 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$		400 Note 1	kHz
				100 Note 1	kHz
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 100 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$		100 Note 1	kHz
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$		100 Note 1	kHz
Hold time when SCLr = "L"	t∟ow		1200		ns
		$\label{eq:VDD} \begin{split} & 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ & 2.3 \ V \leq V_b \leq 2.7 \ V, \\ & C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1200		ns
			4600		ns
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 100 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$	4600		ns
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_{b} \leq 2.0 \; V, \\ & C_{b} = 100 \; pF, \; R_{b} = 5.5 \; k\Omega \end{split}$	4600		ns
Hold time when SCLr = "H"	tніgн		620		ns
		$\label{eq:VD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 50 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$	500		ns
			2700		ns
		$\label{eq:VD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 100 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$	2400		ns
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_{b} \leq 2.0 \; V, \\ & C_{b} = 100 \; pF, \; R_{b} = 5.5 \; k\Omega \end{split}$	1830		ns



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(2/2)

Parameter	Symbol	Conditions	HS (high-speed m	HS (high-speed main) mode		
			MIN.	MAX.		
Data setup time (reception)	tsu:dat		1/fмск + 340 Note 2		ns	
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	1/f _{MCK} + 340 Note 2		ns	
			1/fмск + 760 Note 2		ns	
		$\label{eq:VD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	1/fмск + 760 Note 2		ns	
		$\label{eq:VD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	1/fмск + 570 Note 2		ns	
Data hold time (transmission)	thd:dat		0	770	ns	
		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	770	ns	
			0	1420	ns	
		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; p\text{F}, \; R_b = 2.7 \; k\Omega \end{array}$	0	1420	ns	
		$\begin{array}{l} 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 100 \; p\text{F}, \; R_b = 5.5 \; k\Omega \end{array}$	0	1215	ns	

Note 1. The value must also be equal to or less than fMCK/4.

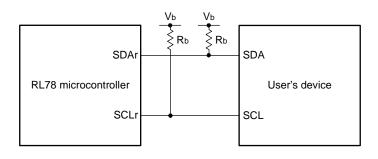
Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the N-ch open drain output (VDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

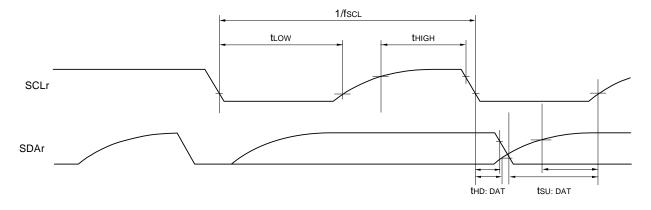
(Remarks are listed on the next page.)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remark 1.** Rb [Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb [F]: Communication line (SDAr, SCLr) load capacitance, Vb [V]: Communication line voltage
- **Remark 2.** r: IIC number (r = 00, 01), g: PIM, POM number (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0), mn = 00, 01)



2.6 Analog Characteristics

2.6.1 Programmable gain instrumentation amplifier and 24-bit ΔΣ A/D converter

(1) Analog input in differential input mode

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dofr = 0 mV, VCOM = 1.0 V, external clock input used)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Full-scale differential input voltage range	Vid	$V_{ID} = (PGAxP - PGAxN) (x = 0 to 3)$		± 800 /Gtotal		mV
Input voltage range	Vı	Each of PGAxP and PGAxN pins (x = 0 to 3)	0.2		1.8	V
Common mode input voltage	Vсом	dofr = 0 mV	0.2+(Vid x Gset1)/2		1.8-(Vid x Gset1)/2	V
Input bias current	lin	VI = 1.0 V			±50	nA
Input offset current	linofr	VI = 1.0 V			±20	nA

(2) Analog input in single-ended input mode

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dofr = 0 mV, VCOM = 1.0 V, external clock input used)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage range		Each of PGAxP and PGAxN pins (x = 0 to 3) GSET1 = 1, GSET2 = 1	0.2		1.8	V
Input bias current	lin	VI = 1.0 V			±50	nA

(3) Programmable gain instrumentation amplifier and 24-bit $\Delta\Sigma$ A/D converter

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dorr = 0 mV, Vcom = 1.0 V, external clock input used, in differential input mode) (1/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES				24	bit
Sampling frequency	fS1	Normal mode		1		MHz
	fS2	Low power mode		0.125		MHz
Output data rate	fdata1	Normal mode	0.48828		15.625	ksps
	fdata2	Low power mode	61.03615		1953.125	sps
Gain setting range	GTOTAL	GTOTAL = GSET1 × GSET2	1		64	V/V
1st gain setting range	GSET1	In differential input mode only		1, 2, 3, 4, 8		V/V
2nd gain setting range	GSET2	In differential input mode only		1, 2, 4, 8		V/V
Offset adjustment bit range	doffb			5		bit
Offset adjustment range	dofr	Referred to input	-164/GSET1		+164/GSET1	mV
Offset adjustment steps	dofs	Referred to input		11/GSET1		mV



(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, normal mode: fs1 = 1 MHz, FDATA	A1 = 3.90625
ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dorr = 0 mV, V	сом = 1.0 V,
external clock input used, in differential input mode)	(2/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Gain error	Eg	TA = 25°C GSET1 = 1, GSET2 = 1 Excluding SBIAS error		±0.2	±2.7	%
		TA = 25°C GSET1 = 8, GSET2 = 4 Excluding SBIAS error		±0.1		%
Gain drift ^{Note}	dEG	Gset1 = 1, Gset2 = 1 Excluding SBIAS drift		(5.6)	(22.0)	ppm/°C
		GSET1 = 8, GSET2 = 4 Excluding SBIAS drift		(9.1)		ppm/°C
Offset error	Eos	TA = 25°C GSET1 = 1, GSET2 = 1 Referred to input		±0.32	±2.90	mV
		TA = 25°C GSET1 = 8, GSET2 = 4 Referred to input		±0.03		mV
Offset drift Note	dEos	GSET1 = 1, GSET2 = 1 Referred to input		(±0.02)	(±6.00)	µV/∘C
		GSET1 = 8, GSET2 = 4 Referred to input		(±0.02)		µV/°C
SND ratio	SNDR	GSET1 = 1, GSET2 = 1, fIN = 50 Hz Normal mode, pin = -1 dBFS	(82)	(85)		dB
		GSET1 = 8, GSET2 = 4, fIN = 50 Hz Normal mode, pin = -1 dBFS	(73)	(80)		dB
Noise	Vn	GSET1 = 1, GSET2 = 1, OSR = 2048		(13)		μVRms
		GSET1 = 8, GSET2 = 4, OSR = 2048		(0.6)		μVRms
Integral non-linearity error	INL	GSET1 = 1, GSET2 = 1, OSR = 2048		(±10)		ppmFS
Common mode rejection ratio	CMRR	VCOM = 1.0±0.8 V, fin = 50 Hz GSET1 = 1, GSET2 = 1 Differential input mode	(72)	(90)		dB
Power supply rejection ratio	PSRR	AVDD = 2.7 to 5.5 V GSET1 = 1, GSET2 = 1 Differential input mode		(85)		dB
ΔΣ A/D converter input clock frequency	fadc		3.8	4	4.2	MHz

 Note
 Calculate the gain drift and offset drift by using the following expression (for 105°C products):

 For gain drift: (MAX(EG(T(-40) to T(105))) - MIN(EG(T(-40) to T(105)))) / (105°C -(-40°C))

 For offset drift: (MAX(Eos(T(-40) to T(105))) - MIN(Eos(T(-40) to T(105)))) / (105°C - (-40°C))

 MAX(EG(T(-40) to T(105))): The maximum value of gain error when the temperature range is -40°C to 105°C

 MIN(EG(T(-40) to T(105))): The maximum value of offset error when the temperature range is -40°C to 105°C

 MAX(Eos(T(-40) to T(105))): The maximum value of offset error when the temperature range is -40°C to 105°C

 MIN(Eos(T(-40) to T(105))): The minimum value of offset error when the temperature range is -40°C to 105°C

 MIN(Eos(T(-40) to T(105))): The minimum value of offset error when the temperature range is -40°C to 105°C

Remark In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.



2.6.2 Sensor power supply (SBIAS)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output voltage range	Vout		0.5		2.2	V
Output voltage setting steps	VSTEP			0.1		V
Output voltage precision	VA	IOUT = 1 mA	(-3)		(+3)	%
Maximum output current	Ιουτ		5			mA
Short circuit current	ISHORT	Vout = 0 V		40	65	mA
Load regulation	Lr	$1 \text{ mA} \le I_{OUT} \le 5 \text{ mA}$			(15)	mV
Power supply rejection ratio	PSRR	AVDD = 5.0 V + 0.1 Vpp ripple f = 100 Hz, IOUT = 2.5 mA	(45)	(50)		dB

Remark In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

2.6.3 Temperature sensor

1	$T_{A} = -40 \text{ to } \pm 105^{\circ}\text{C}$	27V < ΔVη	u = Vnn < 5 5 V	AVss = Vss = 0 V)
١.	1A = -40 10 + 103 C,	\mathbf{Z} . $\mathbf{V} \geq \mathbf{A}\mathbf{V}\mathbf{D}\mathbf{L}$	$\mathbf{v} = \mathbf{v} \mathbf{D} \mathbf{D} \ge \mathbf{J} \cdot \mathbf{J} \cdot \mathbf{v},$	$Av_{33} = v_{33} = 0 v_j$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature coefficient for sensor	TCSNS			(756)		µV/∘C
Sensor output voltage	VTEMP	TA = 25°C		226.4		mV

Remark In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.



2.6.4 A/D converter characteristics

(1) When positive reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), negative reference voltage (-) = AVss (ADREFM = 0), pins subject to A/D conversion: ANI0 to ANI9 and SBIAS

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = AVDD, negative reference voltage (-) = AVss)

Parameter	Symbol	Co	nditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		10	bit
Overall error Note 1	AINL	10-bit resolution	$4.0 \text{ V} \leq \text{AV}_{\text{DI}}$	$b \le 5.5 \text{ V}$		1.2	±6.5	LSB
		ANI0 to ANI9, SBIAS	$2.7 \text{ V} \leq \text{AV}_{\text{D}}$	$b \leq 5.5 \text{ V}$		1.2	±7.0	LSB
Conversion time	t CONV	10-bit resolution	$4.0 \text{ V} \leq \text{AV}_{\text{D}}$	$b \leq 5.5 \text{ V}$	2.125		39	μs
			$2.7 \text{ V} \leq \text{AV}_{\text{D}}$	$b \leq 5.5 \text{ V}$	3.1875		39	μS
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	$4.0 \text{ V} \leq \text{AV}_{\text{D}}$	$b \leq 5.5 \text{ V}$			±0.50	%FSR
		ANI0 to ANI9, SBIAS	$2.7 \text{ V} \leq \text{AV}_{\text{D}}$	$b \leq 5.5 \text{ V}$			±0.60	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution	$4.0 \text{ V} \leq \text{AV}_{\text{D}}$	$b \leq 5.5 \text{ V}$			±0.50	%FSR
		ANI0 to ANI9, SBIAS	$2.7 \text{ V} \leq \text{AV}_{\text{D}}$	$b \leq 5.5 \text{ V}$			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$4.0 \text{ V} \leq \text{AV}_{\text{D}}$	$b \leq 5.5 \text{ V}$			±3.5	LSB
		ANI0 to ANI9, SBIAS	$2.7 \text{ V} \leq \text{AV}_{\text{D}}$	$b \leq 5.5 \text{ V}$			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.7 \text{ V} \leq \text{AV}_{\text{D}}$	$b \le 5.5 \text{ V}$			±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI9	•		AVss		AVDD	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Caution The number of pins depends on the product. For details, see a list of pin functions.

(2) When positive reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), negative reference voltage (-) = AVss (ADREFM = 0), pins subject to A/D conversion: ANI0 to ANI9 and SBIAS

(TA = -40 to +105°C, 2.7 V ≤ AVDD = VDD ≤ 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = VBGR, negative reference voltage (-) = AVss)

Parameter	Symbol	Co	nditions	MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	tсому	8-bit resolution	$2.7~V \leq AV_{\text{DD}} \leq 5.5~V$	17		39	μS
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	$2.7~V \leq AV_{\text{DD}} \leq 5.5~V$			±0.60	%FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.7~V \leq AV_{\text{DD}} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.7~V \le AV_{\text{DD}} \le 5.5~V$			±1.0	LSB
Internal reference voltage (+)	Vbgr	$2.7 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V} \qquad $		3	V		
Analog input voltage	Vain	ANI0 to ANI9	·	0		Vbgr	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. See the Internal reference voltage characteristics.

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2.6.5 12-bit D/A converter

(1) When positive reference voltage (+) = AVDD (DACVRF = 0)

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = AVDD)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	DARES				(12)	bit
Output voltage range	DAOUT	12-bit resolution	0.35		AVDD-0.47	V
Integral non-linearity error	DAILE	12-bit resolution			±4.0	LSB
Differential non-linearity error	DADLE	12-bit resolution			±1.0	LSB
Offset error	DAErr	12-bit resolution			±30	mV
Gain error	DAEG	12-bit resolution			±20	mV
Settling time	DAtset	12-bit resolution, CL = 50 pF, RL = 10 k Ω			(60)	μs

Remark 1. In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment. **Remark 2.** The 12-bit D/A converter characteristics are the values obtained with the configurable amplifier connected.

(2) When positive reference voltage (+) = internal reference voltage (DACVRF = 1)

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = VREFDA)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	DARES				(8)	bit
Internal reference voltage	VREFDA	8-bit resolution	1.34	1.45	1.54	V
Output voltage range	DAOUT	8-bit resolution	0.35		VREFDA	V
Integral non-linearity error	DAILE	8-bit resolution			±1.0	LSB
Differential non-linearity	DADLE	8-bit resolution			±1.0	LSB
error						
Offset error	DAErr	8-bit resolution			±30	mV
Gain error	DAEG	8-bit resolution			±20	mV
Settling time	DAtset	8-bit resolution, CL = 50 pF, RL = 10 k Ω			(60)	μs

Remark 1. In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

Remark 2. The 12-bit D/A converter characteristics are the values obtained with the configurable amplifier connected.

Remark 3. Offset error and gain error do not include error in the internal reference voltage.



2.6.6 Configurable amplifier

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, VCOM = 1/2 AVDD, internally connected voltage follower)

AMP0 configuration SW setting: Positive (+) pin = ANX1, negative (-) pin = ANX0 AMP1 configuration SW setting: Positive (+) pin = ANX3, negative (-) pin = ANX2 AMP2 configuration SW setting: Positive (+) pin = ANX5, negative (-) pin = ANX4

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage	Vin		AVss		AVdd	V
Output voltage	Vol	IL= -1 mA, AV _{DD} = 2.7 to 5.5 V		AVss +0.02	AVss +0.07	V
	Vон	IL= 1 mA, AV _{DD} = 2.7 to 5.5 V	AV _{DD} -0.15	AV _{DD} -0.02		V
Maximum output current	Іоит	$4.5~V \leq AV_{DD} \leq 5.5~V$	±10			mA
		$2.7~V \leq AV_{DD} \leq 5.5~V$	±5			mA
Input-referred offset voltage	Voff	TA = 25°C without trimming IL = 0 mA, VCOM = 1.0 V		±1	±4	mV
		$T_A = 25^{\circ}C$ with trimming IL = 0 mA, VCOM = 1.0 V			±0.35	mV
Temperature coefficient for inputreferred offset voltage	Vотс	I∟ = 0 mA		(±2)	(±8)	µV/∘C
Slew rate	SR1	Normal mode CL = 50 pF, RL = 10 kΩ		(0.1)		V/µs
	SR2	High-speed mode $CL = 50 \text{ pF, } RL = 10 \text{ k}\Omega$		(0.8)		V/µs
Gain bandwidth	GBW1	Normal mode C∟ = 50 pF, R∟ = 10 kΩ		(350)		kHz
	GBW2	High-speed mode CL = 50 pF, RL = 10 k Ω		(1.8)		MHz
Phase margin	θM1	Normal mode C∟ = 50 pF, R∟ = 10 kΩ		(70)		deg
	θ M 2	High-speed mode C∟ = 50 pF, R∟ = 10 kΩ		(60)		deg
Settling time	tset1	Normal mode CL = 50 pF, RL = 10 kΩ		(20)		μs
	tset2	High-speed mode $CL = 50 \text{ pF, } RL = 10 \text{ k}\Omega$		(10)		μs
Peak-to-peak voltage noise	Enb	0.1 to 10 Hz Normal mode CL = 50 pF, RL = 10 kΩ		(2.0)		µVrms
Input-referred noise	En	f = 1 kHz, Normal mode C∟ = 50 pF, R∟ = 10 kΩ		(70)		nV/√Hz
Common mode rejection ratio	CMRR	f = 1 kHz, CL = 50 pF, RL = 10 kΩ		(70)		dB
Power supply rejection ratio	PSRR	2.7 V \leq AVdd \leq 5.5 V f = 1 kHz, CL = 50 pF, RL = 10 k\Omega		(62)		dB

(Remarks are listed on the next page.)



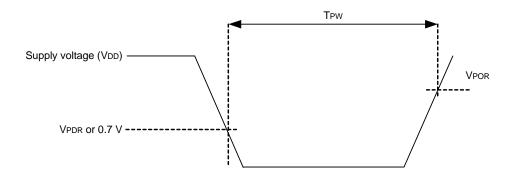
- Remark 1. In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.
- **Remark 2.** The TYP. conditions are the conditions when TA = $25^{\circ}C$ and AVDD = 5.0 V.
- Remark 3. Unless otherwise specified, offset trimming has proceeded.
- Remark 4. Unless otherwise specified, values are for operation in normal mode.

2.6.7 POR characteristics

(TA = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power on/down reset threshold	VPOR	Voltage threshold on VDD rising	1.48	1.56	1.62	V
	VPDR	Voltage threshold on VDD falling Note 1	1.47	1.55	1.61	V
Minimum pulse width Note 2	TPW		300			μS

- **Note 1.** However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 2.4 AC Characteristics.
- **Note 2.** Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





2.6.8 LVD characteristics

(1) LVD detection voltage in reset mode and interrupt mode

Pa	rameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Voltage detection	Supply voltage level	VLVD0	Rising edge	4.62	4.74	4.84	V
threshold			Falling edge	4.52	4.64	4.74	V
		VLVD1	Rising edge	4.50	4.62	4.72	V
			Falling edge	4.40	4.52	4.62	V
		VLVD2	Rising edge	4.30	4.42	4.51	V
			Falling edge	4.21	4.32	4.41	V
		Vlvd3	Rising edge	3.13	3.22	3.29	V
			Falling edge	3.07	3.15	3.22	V
		VLVD4	Rising edge	2.95	3.02	3.09	V
			Falling edge	2.89	2.96	3.02	V
		Vlvd5	Rising edge	2.74	2.81	2.87	V
			Falling edge	2.68	2.75	2.81	V
		VLVD6	Rising edge	2.55	2.61	2.67	V
			Falling edge	2.49	2.55	2.61	V
Minimum pulse wie	dth	t∟w		300			μs
Detection delay tin	ne					300	μS

(2) LVD detection voltage in interrupt & reset mode

(TA = -40 to +105°C, VPDR \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol		Con	ditions	MIN.	TYP.	MAX.	Unit
Voltage detection	VLVDD6	VPOC2,	VPOC1, VPOC0 = 0, 0, 0, f	alling reset voltage	2.49	2.55	2.61	V
threshold	VLVDD4		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.95	3.02	2.61 3.09 3.02 3.29 3.22 2.81 4.51 4.41 2.81 4.72 4.62 2.81 3.29 3.22	V
				Falling interrupt voltage	2.89	2.96	3.02	V
	VLVDD3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.13	3.22	3.29	V
				Falling interrupt voltage	3.07	3.15	3.22	V
	VLVDD5	VPOC2,	VPOC1, VPOC0 = 0, 0, 1, falling reset voltage		2.68	2.75	2.81	V
	VLVDD2		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	4.30	4.42	4.51	V
				Falling interrupt voltage	4.21	4.32	4.41	V
	VLVDD5	VPOC2,	VPOC1, VPOC0 = 0, 1, 0, f	alling reset voltage	2.68	2.75	2.81	V
	VLVDD1		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	4.50	4.62	4.72	V
				Falling interrupt voltage	4.40	4.52	4.62	V
	VLVDD5	VPOC2,	VPOC1, VPOC0 = 0, 1, 1, f	alling reset voltage	2.68	2.75	2.81	V
	VLVDD3		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	3.13	3.22	3.29	V
				Falling interrupt voltage	3.07	3.15	3.22	V
	VLVDD0		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	4.62	4.74	4.84	V
				Falling interrupt voltage	4.52	4.64	4.74	V

2.6.9 Power supply voltage rising slope characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				50	V/ms

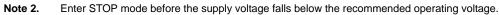
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 2.4 AC Characteristics.

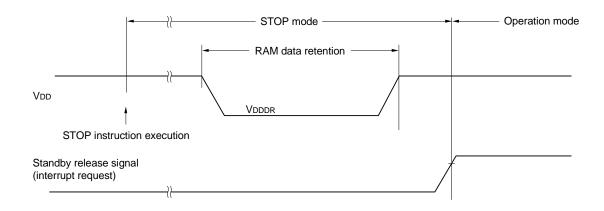
<R> 2.7 RAM Data Retention Characteristics

(TA = -40 to +105°C, Vss = 0 V))

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	Vdddr		1.47 Notes 1, 2		5.5	V

Note 1. The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.





2.8 Flash Memory Programming Characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	$2.4~V \leq V_{DD} \leq 5.5~V$	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C ^{Note 4}	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°C ^{Note 4}		1,000,000		
		Retained for 5 years TA = 85°C ^{Note 4}	100,000			
		Retained for 20 years TA = 85°C ^{Note 4}	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

Note 4. This temperature is the average value at which data are retained.

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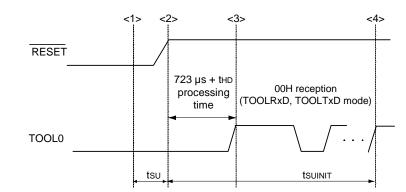
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2.9 Dedicated Flash Memory Programmer Communication (UART)

Parameter	Symbol	mbol Conditions		TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

2.10 Timing for Switching Flash Memory Programming Modes

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)										
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit				
How long from when an external reset ends until the initial communication settings are specified	tsuini⊤	POR and LVD reset must end before the external reset ends.			100	ms				
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μS				
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	thd	POR and LVD reset must end before the external reset ends.	1			ms				



<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the external reset ends).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit. The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends

tHD: How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)



3. ELECTRICAL SPECIFICATIONS (M: TA = -40 to +125°C)

This chapter describes the electrical specifications for the products "M: Industrial applications (TA = -40 to +125°C)".

- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Alternate functions other than AFE in the RL78/I1E User's Manual.
- Caution 3. Please contact Renesas Electronics sales office for derating of operation under TA = +85 to +125°C. Derating is the systematic reduction of load for the sake of improved reliability.
- **Remark** The electrical characteristics of the products M: Industrial applications (TA = -40 to +125°C) are different from those of the products "G: Industrial applications". For details, refer to **3.1** to **3.10**.



3.1 **Absolute Maximum Ratings**

Absolute Maximum R	atings				(1/2)
Parameter	Symbol	Conc	litions	Ratings	Unit
Supply voltage	Vdd			-0.5 to +6.5	V
	AVdd	AVDD = VDD		-0.5 to +6.5	V
	AVss	AVss = Vss		-0.5 to +0.3	V
REGC pin input voltage	Viregc	REGC		-0.3 to +2.8 and -0.3 to VDD + 0.3 ^{Note 1}	V
REGA pin input voltage	Virega	REGA		-0.3 to +2.8 and -0.3 to AV _{DD} + 0.3 ^{Note 2}	V
Input voltage	VI1	P10 to P15, P40, P121 RESET	P10 to P15, P40, P121, P122, P137, EXCLK, RESET		V
Alternate-function pin	VI2	P16, P17, P41, P42	Digital input voltage	-0.3 to VDD + 0.3 Note 3	V
input voltage		(36-pin products only)	Analog input voltage	-0.3 to AVDD + 0.3 Note 3	V
Analog input voltage	VIA	PGA0P to PGA3P, PG ANI0 to ANI9, ANX0 to	·	-0.3 to AVDD + 0.3 Note 3	V
Output voltage	V01	P10 to P15, P40		-0.3 to VDD + 0.3 Note 3	V
Alternate-function pin	VO2	P16, P17, P41, P42	Digital output voltage	-0.3 to VDD + 0.3 Note 3	V
output voltage		(36-pin products only)	Analog output voltage	-0.3 to AVDD + 0.3 Note 3	V
Analog output voltage	VOA	SBIAS, AMP0O to AM	P2O, ANX0 to ANX5	-0.3 to AVDD + 0.3 Note 3	V

Absolute Maximum Ratings

Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Connect the REGA pin to AVss via a capacitor (0.22 µF). This value regulates the absolute maximum rating of the REGA pin. Do not use this pin with voltage applied to it.

- Note 3. Must be 6.5 V or lower.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Remark 2. Vss is used as the reference voltage.



Absolute Maximum Ratings

(2/2)Parameter Conditions Unit Symbol Ratings P10 to P17, P40 to P42 Output current, high IOH1 Per pin -40 mΑ Total of all pins P10 to P17, P41, P42 Note -100 mΑ Analog output current, Іона Per pin AMP0O to AMP2O -12 mΑ ANX0 to ANX5 -0.12 high mΑ Total of all pins AMP0O to AMP2O, ANX0 to ANX5 -18 mΑ Output current, low **I**OL1 Per pin P10 to P17, P40 to P42 40 mΑ Total of all pins 100 P10 to P17, P41, P42 Note mΑ Analog output current, low IOLA Per pin AMP0O to AMP2O 12 mΑ ANX0 to ANX5 0.12 mΑ Total of all pins AMP0O to AMP2O, ANX0 to ANX5 18 mΑ °C ΤA Operating ambient In normal operation mode -40 to +125 temperature In flash memory programming mode Storage temperature -65 to +150 °C Tstg

Note This indicates the total current value when P16, P17, P41, and P42 are used as digital input pins.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins. Remark 2. Vss is used as the reference voltage.



3.2 Oscillator Characteristics

3.2.1 X1 characteristics

RL78/I1E

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7~V \leq V \text{DD} \leq 5.5~V$	1.0		20.0	MHz
	crystal resonator	$2.4~\text{V} \leq \text{Vdd} < 2.7~\text{V}$	1.0		16.0	

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- Remark When using the X1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/I1E User's Manual..

3.2.2 On-chip oscillator characteristics

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency	fін	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	1		24	MHz
Notes 1, 2		$2.4 \text{ V} \leq \text{Vdd} < 2.7 \text{ V}$	1		16	MHz
High-speed on-chip oscillator clock frequency		-40 to +105°C	-2.0		+2.0	%
accuracy		+105 to +125°C	-3.0		+3.0	%
Low-speed on-chip oscillator clock frequency	fı∟			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 3 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.



3.2.3 PLL characteristics

(TA = -40 to +125°C	2.4 V < AVDD = VDD < 5	5.5 V, AVss = Vss = 0 V)
	,	$n_{0} = 1, n_{100} = 100 = 0.1$

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
PLL output frequencyNotes 1, 2,	fpll	fmx = 8 MHz	DSFRDIV = 0	DSCM = 0		48		MHz
3			DSFRDIV = 1	DSCM = 0		24		MHz
				DSCM = 1		32		MHz
		fmx = 4 MHz	DSFRDIV = 0	DSCM = 0		24		MHz
				DSCM = 1		32		MHz
Lockup wait time		Time from whe phase is locked	Fime from when PLL output is enabled to when the obase is locked					μs
Interval wait time			ime from when the PLL stops operating to when the etting to start PLL operation is specified					μs
Setup wait time		•		input clock stabilizes to when the PLL is	1			μs

Note 1. When using a PLL, input a clock of 4 MHz or 8 MHz to the PLL.

Note 2. Be sure to specify one of these settings when using a PLL.

Note 3. When using the PLL output as the CPU clock, fin is divided by 2, 4, or 8 according to the setting of the RDIV1 and RDIV0 bits.



(1/3)

3.3 DC Characteristics

3.3.1 Pin characteristics

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Item	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P10 to P17 and P40 to	$4.0~V \leq V \text{DD} \leq 5.5~V$			-3.0 Note 3	mA
		P42 Note 2	$2.4~\text{V} \leq \text{VDD} < 4.0~\text{V}$			-1.0 Note 3	mA
		Note 3 (When duty < 70% Note 4)	$4.0~V \leq V \text{DD} \leq 5.5~V$			-30.0	mA
			$2.7~\text{V} \leq \text{Vdd} < 4.0~\text{V}$			-19.0	mA
			$2.4~\text{V} \leq \text{VDD} < 2.7~\text{V}$			-10.0	mA
Output current, low Note 1	IOL1	Per pin for P10 to P17 and P40 to P42 Note 2	$4.0~V \leq V \text{DD} \leq 5.5~V$			8.5 Note 3	mA
			$2.7~\text{V} \leq \text{Vdd} < 4.0~\text{V}$			1.5 Note 3	mA
			$2.4~\text{V} \leq \text{VDD} < 2.7~\text{V}$			0.6 Note 3	mA
		Total of P10 to P17, P41, and P42	$4.0~V \leq V \text{DD} \leq 5.5~V$			40.0	mA
		Note 2	$2.7~\text{V} \leq \text{Vdd} < 4.0~\text{V}$			35.0	mA
		(When duty \leq 70% ^{Note 4})	$2.4~\text{V} \leq \text{Vdd} < 2.7~\text{V}$			20.0	mA

Note 1.Value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin.Note 2.This indicates the total current value when P16, P17, P41, and P42 are used as digital I/O ports. When using these pins

as analog function (AFE) pins, refer to 3.1 Absolute Maximum Ratings.

Note 3. Do not exceed the total current value.

Note 4. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$

Example: n = 80% when IOH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P10 to P15 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(1A = -40 10 + 125 C)	, 2. 4 V ≥ /	$AVDD = VDD \ge 3.$	5 v, AVSS = VSS = 0 v)				(2/3)
Item	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P10 to P17 and P40 to P42	Normal input buffer	0.8 Vdd		Vdd	V
	VIH2	P11, P12, P14,	TTL input buffer, 4.0 V \leq VDD \leq 5.5 V	2.2		Vdd	V
		P15	TTL input buffer, 3.3 V \leq VDD < 4.0 V	2.0		Vdd	V
			TTL input buffer, 2.4 V \leq VDD < 3.3 V	1.28		Vdd	V
	Vінз	P121, P122, P137, EXCLK, RESET				Vdd	V
Input voltage, low	VIL1	P10 to P17 and P40 to P42	Normal input buffer	0		0.2 Vdd	V
	VIL2	P11, P12, P14,	TTL input buffer, 4.0 V \leq VDD \leq 5.5 V	0		0.8	V
		P15	TTL input buffer, 3.3 V \leq VDD < 4.0 V	0		0.5	V
			TTL input buffer, 2.4 V \leq VDD < 3.3 V	0		0.32	V
	VIL3	P121, P122, P13	7, EXCLK, RESET	0		0.2 Vdd	V
Output voltage, high	VOH1	P10 to P17 and	$4.0~V \leq V\text{DD} \leq 5.5~V\text{, IOH1}$ = -3.0 mA	Vdd - 0.7			V
		P40 to P42	$2.4 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$, Ioh1 = -1.0 mA	Vdd - 0.5			V
Output voltage, low	VOL1	P10 to P17 and	$4.0~V \leq V_{DD} \leq 5.5~V,~IOL1 = 8.5~mA$			0.7	V
		P40 to P42	$2.7~V \leq V\text{DD} \leq 5.5~V,~\text{IOL1} = 1.5~m\text{A}$			0.5	V
			$2.4~V \leq V_{DD} \leq 5.5~V,~IOL1 = 0.6~mA$			0.4	V

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(2/3)

 $\label{eq:caution} Caution \qquad \mbox{The maximum ViH value on P10 to P15 is VDD, even in the N-ch open-drain mode.}$

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Remark

	•, =	AVDD = VDD - 3.3 V, AV33 =	,		i	i	i	(3/3)
Item	Symbol	Cond	ditions		MIN.	TYP.	MAX.	Unit
Input leakage	ILIH1	P10 to P17, and P40 to P42	VI = VDD	VI = VDD			1	μΑ
current, high	Ілн2	P137, RESET	VI = VDD				1	μΑ
	Ішнз	P121, P122 (X1, X2, EXCLK)	X1, X2, EXCLK) VI = VDD	In input port mode or when using external clock input			1	μA
				When a resonator is connected			10	μΑ
Input leakage	ILIL1	P10 to P17, and P40 to P42	VI = VSS	VI = VSS			-1	μΑ
current, low	ILIL2	P137, RESET	VI = VSS				-1	μΑ
	ILIL3	P121, P122 (X1, X2, EXCLK)	VI = VSS	In input port mode or when using external clock input			-1	μΑ
				When a resonator is connected			-10	μA
On-chip pull-up resistance	Ru	P10 to P15, P40	VI = VSS, ir	n input port mode	10	20	100	kΩ

Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(3/3)



(1/2)

RL78/I1E

3.3.2 Supply current characteristics

(1A - 40 to + 125 to , 2.4 to - 400 - 400 - 3.5 to , At 35 - 0.4)								(1/2)										
Parameter	Symbol		Conditions			MIN.	TYP.	MAX.	Unit									
Supply	IDD1	Operating	fHOCO = 24 MHz, fMAIN = 24 MHz Note 3	Basic	VDD = 5.0 V		1.7		mA									
current		mode ^{Note 2}		operation	Vdd = 3.0 V		1.7											
Note 1			fHOCO = 24 MHz, fMAIN = 24 MHz Note 3	Normal	VDD = 5.0 V		3.8	7.6	mA									
				operation	VDD = 3.0 V		3.8	7.6										
			fHOCO = 16 MHz, fMAIN = 16 MHz Note 3	Normal	VDD = 5.0 V		2.8	5.6										
				operation	VDD = 3.0 V		2.8	5.6										
			fmx = 20 MHz, fmain = 20 MHz Note 4,	Normal	Square wave input		3.3	6.5	mA									
		VDD = 5.0 V	operation	Resonator connection		3.5	6.6											
			$f_{MX} = 20 \text{ MHz}$, $f_{MAIN} = 20 \text{ MHz} \text{ Note } 4$,	Normal	Square wave input		3.3	6.5										
													$V_{DD} = 3.0 V$	operation	Resonator connection		3.5	6.6
			fmx = 10 MHz, fmain = 10 MHz Note 4,	Normal	Square wave input		2.0	3.9										
			VDD = 5.0 V	operation	Resonator connection		2.1	4.0										
			$f_{MX} = 10 \text{ MHz}$, $f_{MAIN} = 10 \text{ MHz}$ Note 4,	Normal	Square wave input		2.0	3.9										
			$V_{DD} = 3.0 V$	operation	Resonator connection		2.1	4.0										
			$f_{MX} = 8 \text{ MHz}, f_{MAIN} = 24 \text{ MHz} \text{ Note } 5,$	Normal	Square wave input		5.1	10.4	mA									
	V	VDD = 5.0 V	operation	Resonator connection		5.2	10.5											
			$f_{MX} = 8 \text{ MHz}, f_{MAIN} = 24 \text{ MHz} \text{ Note 5},$	Normal	Square wave input		5.1	10.4										
			VDD = 3.0 V	operation	Resonator connection		5.2	10.5										

 $(TA = -40 \text{ to } +125^{\circ}C, 2.4 \text{ V} \le \text{AVDD} = \text{VDD} \le 5.5 \text{ V}, \text{AVss} = \text{Vss} = 0 \text{ V})$

- **Note 1.** Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the RTC, interval timer, watchdog timer, LVD circuit, AFE, I/O ports, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. The relationship between the operation voltage range and the CPU operating frequency is as below.

2.7 V \leq VDD \leq 5.5 V @ 1 MHz to 24 MHz

2.4 V \leq VDD \leq 5.5 V @ 1 MHz to 16 MHz

- Note 3. When the high-speed system clock is stopped
- Note 4. When the high-speed on-chip oscillator and the PLL are stopped
- Note 5. When the high-speed on-chip oscillator is stopped and the PLL is operating

Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency
- Remark 3. fMAIN: Main system clock frequency
- **Remark 4.** The temperature condition for the TYP. value is $T_A = 25^{\circ}C$



(2|2)

TA = -40 to	+125 C	, ∠. ∓ V ⊇ A	$VDD = VDD \leq 5.5 \text{ V}, \text{ AVSS} = VSS = 0 \text{ V})$		-			(2/2
Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Supply current	Idd2	HALT mode	fhoco = 24 MHz, fmain = 24 MHz Note 4	Vdd = 5.0 V		0.44	3.42	mA
Note 1	Note 2	Note 3		VDD = 3.0 V		0.44	3.42	
			fhoco = 16 MHz, fmain = 16 MHz Note 4	Vdd = 5.0 V		0.40	2.50	
				VDD = 3.0 V		0.40	2.50	
			fmx = 20 MHz, fmain = 20 MHz Note 5, Vdd = 5.0 V	Square wave input		0.28	2.94	mA
				Resonator connection		0.49	3.08	
			fmx = 20 MHz, fmain = 20 MHz ^{Note 5} , Vdd = 3.0 V	Square wave input		0.28	2.94	
				Resonator connection		0.49	3.08	
			fmx = 10 MHz, fmain = 10 MHz ^{Note 5} , Vdd = 5.0 V	Square wave input		0.19	1.54	
				Resonator connection		0.30	1.63	
			fmx = 10 MHz, fmain = 10 MHz Note 5, Vdd = 3.0 V	Square wave input		0.19	1.54	
				Resonator connection		0.30	1.63	
			fmx = 8 MHz, fmain = 24 MHz Note 6 , Vdd = 5.0 V	Square wave input		0.76	3.92	mA
				Resonator connection		0.86	4.04	
			fmx = 8 MHz, fmain = 24 MHz Note 6, Vdd = 3.0 V	Square wave input		0.76	3.92	
				Resonator connection		0.86	4.04	
	Idd3	STOP mode	$T_A = -40^{\circ}C$			0.38	1.14	μΑ
	Note 7		$T_A = +25^{\circ}C$			0.50	1.14	
			$T_A = +50^{\circ}C$			0.66	4.52	
			TA = +70°C			1.04	7.98	
			Ta = +85°C			2.92	16.0	
			$T_A = +105^{\circ}C$			11.0	100.0	
			TA = +125°C			22.0	200.0	

 $(TA = -40 \text{ to } +125^{\circ}C, 2.4 \text{ V} \le \text{AVDD} = \text{VDD} \le 5.5 \text{ V}, \text{AVss} = \text{Vss} = 0 \text{ V})$

Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the RTC, interval timer, watchdog timer, LVD circuit, AFE, I/O ports, and on-chip pull-up/pull-down resistors and the current flowing during writing to the data flash.

- Note 2. During HALT instruction execution from flash memory
- Note 3. The relationship between the operation voltage range and the CPU operating frequency is as below.
 - 2.7 V \leq VDD \leq 5.5 V @ 1 MHz to 24 MHz
 - 2.4 V \leq Vdd \leq 5.5 V @ 1 MHz to 16 MHz
- **Note 4.** When the high-speed system clock is stopped
- Note 5. When the high-speed on-chip oscillator and the PLL are stopped
- Note 6. When high-speed on-chip oscillator is stopped and the PLL is operating
- Note 7. The MAX. value includes the leakage current in STOP mode.
- Remark 1. fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency
- Remark 3. fMAIN: Main system clock frequency
- Remark 4. The temperature condition for the TYP. value is TA = 25°C, except the operation in STOP mode.



• Peripheral functions

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol	Condi	tions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I _{FIL} Note 1				0.20		μΑ
RTC operating current	IRTC Notes 1, 2, 3	f _{MX} = 4 MHz, RTCCL = 00H (f _N	их/122)		22		μΑ
Interval timer operating current	I _{IT} Notes 1, 2, 4	мх = 4 MHz, RTCCL = 00Н (fмх/122)			22		μA
Watchdog timer operating current	I _{WDT} Notes 1, 5, 6	fil = 15 kHz			0.22		μA
LVD operating current	ILVD Notes 1, 7				0.08		μΑ
Self-programming operating current	I _{FSP} Notes 1, 8				2.00	12.20	mA
BGO operating current	I _{BGO} Notes 1, 9				2.00	12.20	mA
SNOOZE operating	I _{SNOZ} Note 1	A/D converter operation	The mode is performed		0.50	1.10	mA
current		Notes 10,	During A/D conversion, AV _{DD} = V _{DD} = 3.0 V		1.20	2.04	
		CSI/UART operation			0.70	1.54	
		DTC operation			3.10		

Note 1. Current flowing to VDD

Note 2. When the high-speed on-chip oscillator is stopped

Note 3. Current flowing only to the real-time clock (RTC). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock is operating in operation mode or HALT mode.

- **Note 4.** Current flowing only to the interval timer. The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the interval timer is operating in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, also add IFIL.
- Note 5. When the high-speed on-chip oscillator and high-speed system clock are stopped.
- **Note 6.** Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).
- The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is operating.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is operating.
- Note 8. Current flowing during self-programming
- Note 9. Current flowing during writing to the data flash
- **Note 10.** The current flowing into the AVDD is included.

Remark 1. fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

- Remark 2. fil: Low-speed on-chip oscillator clock frequency
- **Remark 3.** The temperature condition for the TYP. value is $TA = 25^{\circ}C$



AFE functions

```
(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)
```

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
24-bit $\Delta\Sigma$ A/D converter operating current	Idsad	Normal mode Notes 1, 2 Circuits that operate: ABGR, REGA, SBIAS, VREFAMP, PGA, 24-bit $\Delta\Sigma$ A/D converter, and digital filter Differential input mode OSR = 256 SBIAS IouT = 0 mA		0.94	1.46	mA
		Low power mode Notes 1, 2 Circuits that operate: ABGR, REGA, SBIAS, VREFAMP, PGA, 24-bit $\Delta\Sigma$ A/D converter, and digital filter Differential input mode OSR = 256 SBIAS lout = 0 mA		0.60	0.91	mA
10-bit A/D converter operating current	IADC	During conversion at the highest speed Notes 1, 2 $AV_{DD} = 5.0 V$		1.30	1.70	mA
Configurable amplifier operating current	Іамр	Normal mode Notes 1, 2 Circuits that operate: ABGR and configurable amplifier IL = 0 mA Per channel		0.13	0.24	mA
		High-speed mode Notes 1, 2 Circuits that operate: ABGR and configurable amplifier IL = 0 mA Per channel		0.30	0.45	mA
12-bit D/A converter operating current	Idac	When AV _{DD} and AV _{SS} are selected as the reference voltage Notes 1, 2 Circuits that operate: ABGR and internal reference voltage (VREFDA)		0.61	0.97	mA

Note 1. Current flowing to AVDD

Note 2. Current flowing only to the circuits that operate shown in the Conditions column.



3.4 AC Characteristics

Items	Items Symbol Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	Тсү	Main system clock (fMAIN) operation	$2.7~V \leq V\text{DD} \leq 5.5~V$	0.04167		1	μS
			$2.4~\text{V} \leq \text{VDD} < 2.7~\text{V}$	0.0625		1	μs
		In the self-programming mode	$2.7~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$	0.04167		1	μs
			$2.4~\text{V} \leq \text{VDD} < 2.7~\text{V}$	0.0625		1	μs
External system clock	fEX	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	1	1.0		20.0	MHz
frequency		$2.4 \text{ V} \leq \text{Vdd} < 2.7 \text{ V}$		1.0		8.0	MHz
External system clock	texн,	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$		24			ns
input high-level width, low-level width	texl	$2.4 \text{ V} \leq \text{Vdd} < 2.7 \text{ V}$	60			ns	
TI00 to TI03, TI10, TI11 input high-level width, low-level width	ttiH, tti∟			1/fмск + 10			ns
Timer RJ input cycle	fc	TRJIO0	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	100			ns
			$2.4~\text{V} \leq \text{VDD} < 2.7~\text{V}$	300			ns
Timer RJ input high-	t⊤jiH,	TRJIO0	$2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	40			ns
level width, low-level width	t⊤ji∟		$2.4~\text{V} \leq \text{Vdd} < 2.7~\text{V}$	120			ns
Timer RG input high- level width, low-level width	ttgih, ttgi∟	TRGIOA, TRGIOB		2.5/fclk			ns
TO00 to TO03,	fтo		$4.0~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$			12	MHz
TO10, TO11,			$2.7~\text{V} \leq \text{Vdd} \leq 4.0~\text{V}$			6	MHz
TRJIO0, TRJO0, TRGIOA, TRGIOB output frequency			$2.4 \text{ V} \leq \text{Vdd} < 2.7 \text{ V}$			3	MHz
PCLBUZ0 output	f PCL		$4.0~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$			12	MHz
frequency			$2.7~V \leq V_{DD} \leq 4.0~V$			6	MHz
			$2.4~\text{V} \leq \text{VDD} < 2.7~\text{V}$			3	MHz
Interrupt input high- level width, low-level width	tinth, tintl	INTP1 to INTP7	1	1			μs
RESET low-level width	tRSL			10			μS

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

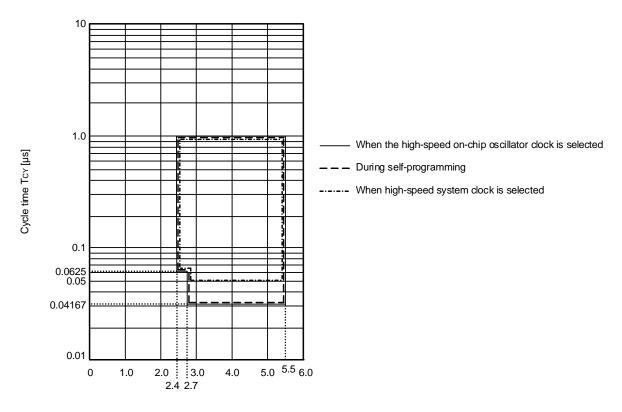
Remark fMCK: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))



TCY vs VDD

Minimum Instruction Execution Time During Main System Clock Operation

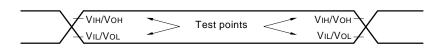


Supply voltage VDD [V]

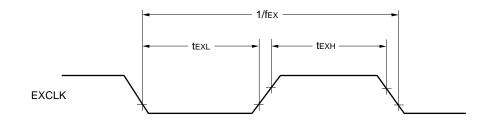
R01DS0274EJ0110 Rev. 1.10 Jun 30, 2016



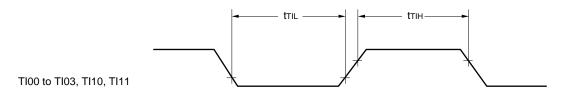
AC Timing Test Points

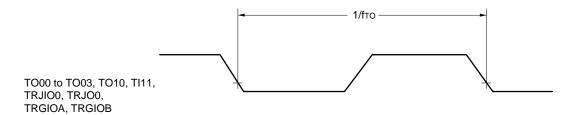


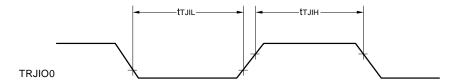
External System Clock Timing



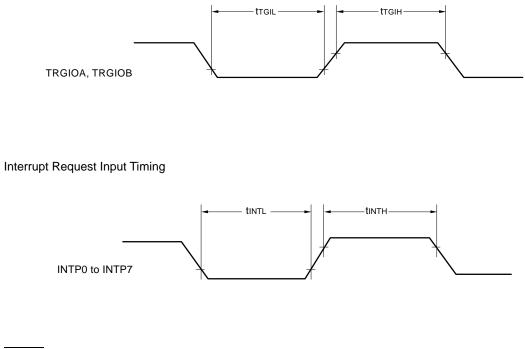
TI/TO Timing



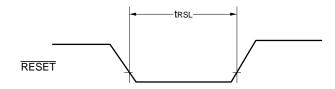








RESET Input Timing





3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	ed main) Mode	Unit
			MIN.	MAX.	
Transfer rate Note 1				fмск/12	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} N_{ote 2}$		2.0	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

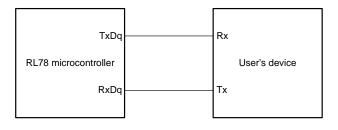
Note 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

24 MHz (2.7 V \leq VDD \leq 5.5 V)

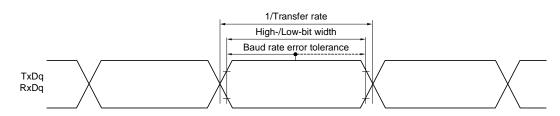
16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0, 1), g: PIM or POM number (g = 1)

Remark 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 02))

n: Channel number (mn = 00 to 03))



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) (TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions		Conditions HS (high-speed ma mode		Unit
				MIN. MAX.		
SCKp cycle time	tkCY1	tксү1 \geq 4/fclk	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	333		ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	666		ns
SCKp high-/low-level width	t кн1, t к∟1	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		tксү1/2 - 24		ns
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		tксү1/2 - 36		ns
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		tксү1/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	tsik1	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$		66		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} \leq 5.5 \ V \\ \\ 2.4 \ V \leq V_{DD} \leq 5.5 \ V \end{array}$		66		ns
				113		ns
SIp hold time (from SCKp↑) Note 1	tksi1			38		ns
Delay time from SCKp \downarrow to SOp output Note 2	tkso1	C = 30 pF Note	e 3		66.6	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM number (g = 1)

Remark 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))



(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions		HS (high-spee	d main) mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 1	tkCY2	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	20 MHz < fмск	16/fмск		ns
			fмск ≤ 20 MHz	12/fмск		ns
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	16 MHz < fмск	16/fмск		ns
			fмск ≤ 16 MHz	12/fмск		ns
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		12/fмск and 1000		ns
SCKp high-/low-level width	tĸн₂, tĸ∟₂	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$		tксү2/2 - 14		ns
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		tксү2/2 - 16		ns
		$2.4~V \leq V_{DD} \leq 5.5~V$		tксү2/2 - 36		ns
SIp setup time (to SCKp [↑]) Note 2	tsik2	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		1/fмск + 40		ns
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 2	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output	tkso2	C = 30 pF Note 4	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		2/fмск + 66	ns
Note 3			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		2/fмск + 113	ns
SSI00 setup time	tssik	DAPmn = 0	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	240		ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	400		ns
		DAPmn = 1	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1/fмск + 240		ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	1/fмск + 400		ns
SSI00 hold time	tkssi	DAPmn = 0	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1/fмск + 240		ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	1/fмск + 400		ns
		DAPmn = 1	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	240		ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	400		ns

Note 1. The maximum transfer rate in the SNOOZE mode is 1 Mbps.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

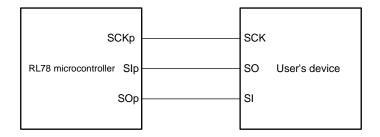
Caution Select the normal input buffer for the SIp and SCKp pins and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM number (g = 1)

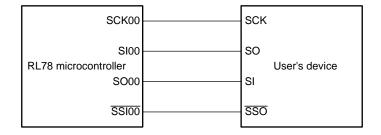
Remark 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))



CSI mode connection diagram (during communication at same potential)

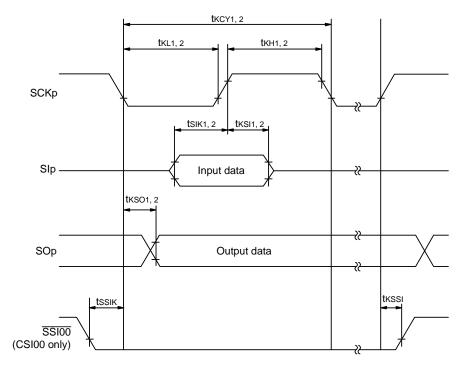


CSI mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))



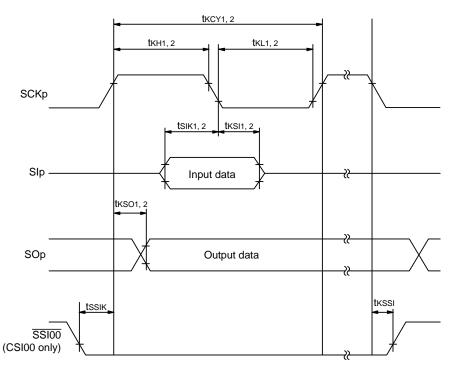
Remark 1. p: CSI number (p = 00, 01) Remark 2. m: Unit number, n: Channel number (mn = 00, 01)





CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01) Remark 2. m: Unit number, n: Channel number (mn = 00, 01)

RENESAS

(4) During communication at same potential (simplified I²C mode)

Parameter	Symbol	Conditions	HS (high-spee	d main) mode	Unit
			MIN.	MIN. MAX.	
SCLr clock frequency	fscL	$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ C_{\text{b}} = 50 \ \text{pF}, \ R_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$		400 Note 1	kHz
		$\label{eq:VDD} \begin{array}{l} 2.4 \ V \leq V_{\text{DD}} \leq 5.5 \ \text{V}, \\ C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 3 \ \text{k}\Omega \end{array}$		100 ^{Note 1}	kHz
Hold time when SCLr = "L"	tLOW	$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ C_{\text{b}} = 50 \ \text{pF}, \ R_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	1200		ns
		$\label{eq:VDD} \begin{split} 2.4 \ V \leq V_{DD} \leq 5.5 \ V, \\ C_b = 100 \ pF, \ R_b = 3 \ k\Omega \end{split}$	4600		ns
Hold time when SCLr = "H"	tніgн	$\label{eq:VDD} \begin{array}{l} 2.7 \mbox{ V} \leq V_{DD} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 2.7 \mbox{ k}\Omega \end{array}$	1200		ns
		$\label{eq:VDD} \begin{split} 2.4 \ V \leq V_{DD} \leq 5.5 \ V, \\ C_b = 100 \ pF, \ R_b = 3 \ k\Omega \end{split}$	4600		ns
Data setup time (reception)	tsu: dat	$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ C_{\text{b}} = 50 \ \text{pF}, \ R_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	1/fмск + 220 Note 2		ns
		$\label{eq:VDD} \begin{array}{l} 2.4 \ V \leq V_{\text{DD}} \leq 5.5 \ \text{V}, \\ C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 3 \ \text{k}\Omega \end{array}$	1/fмск + 580 Note 2		ns
Data hold time (transmission)	thd: dat	$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ C_{\text{b}} = 50 \ \text{pF}, \ R_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	0	770	ns
		$\label{eq:VDD} \begin{split} 2.4 \ V \leq V_{DD} \leq 5.5 \ V, \\ C_b = 100 \ pF, \ R_b = 3 \ k\Omega \end{split}$	0	1420	ns

$(TA = -40 \text{ to } +125^{\circ}C, 2.4 \text{ V} \le \text{AVDD} = \text{VDD} \le 5.5 \text{ V}, \text{AVss} = \text{Vss} = 0 \text{ V})$

Note 1. The value must also be equal to or less than fmck/4.

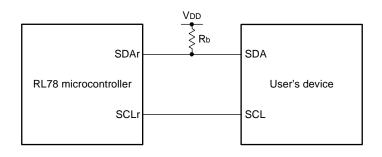
Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

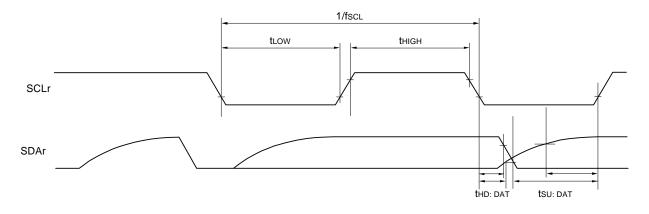
(Remarks are listed on the next page.)



Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remark 1. Rb [Ω]: Communication line (SDAr) pull-up resistance, Cb [F]: Communication line (SDAr, SCLr) load capacitance

Remark 2. r: IIC number (r = 00, 01), g: PIM number (g = 1), h: POM number (h = 1)

Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0, 1), mn = 00, 01)



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(1/2)

Parameter	Symbol		Conditions			HS (high-speed main) mode	
				-	MIN.	MAX.	
Transfer rate		Reception	4.0	$V \leq V_{\text{DD}} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq V_b \leq 4.0 \text{ V}$		fмск/12 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 2$		2.0	Mbps
			2.7	$V \leq V_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \leq V_b \leq 2.7 \text{ V}$		fмск/12 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 2$		2.0	Mbps
			2.4	$V \leq V_{\text{DD}} < 3.3$ V, 1.6 V $\leq V_{b} \leq 2.0$ V		fмск/12 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 2$		2.0	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLk) are:

24 MHz (2.7 V \leq VDD \leq 5.5 V) 16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remark 1. Vb [V]: Communication line voltage

Remark 2. q: UART number (q = 0, 1), g: PIM or POM number (g = 1)

Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01)



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

 $(TA = -40 \text{ to } +125^{\circ}C, 2.4 \text{ V} \le \text{AVDD} = \text{VDD} \le 5.5 \text{ V}, \text{AVss} = \text{Vss} = 0 \text{ V})$

(2/2)

	,		D = 0.0 , $A = 0.0 $ = 0.0 = 0.0 j			(4)	
Parameter	Symbol		Conditions	HS (high-speed main) mode		Unit	
				MIN.	MAX.		
Fransfer rate		Transmission	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V},~2.7~\text{V} \leq \text{V}_{b} \leq 4.0~\text{V}$		Note 1	bps	
			Theoretical value of the maximum transfer rate $C_{\rm b}$ = 50 pF, $R_{\rm b}$ = 1.4 k Ω , $V_{\rm b}$ = 2.7 V		2.0 Note 2	Mbps	
			$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$		Note 3	bps	
			Theoretical value of the maximum transfer rate $C_{\rm b}$ = 50 pF, $R_{\rm b}$ = 2.7 k Ω , $V_{\rm b}$ = 2.3 V		1.2 Note 4	Mbps	
			$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \end{array}$		Note 5	bps	
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 k Ω , V_b = 1.6 V		0.43 Note 6	Mbps	

Note 1. The smaller maximum transfer rate derived by using fMck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq VDD \leq 5.5 V and 2.7 V \leq Vb \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
Baud rate error (theoretical value) =
$$\frac{\frac{1}{Transfer rate \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{Transfer rate}) \times Number of transferred bits}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- Note 2.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- **Note 3.** The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate = -

rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$

1

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 4.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



Note 5. The smaller maximum transfer rate derived by using fMcK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq VDD < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times 100 [\%]}$$

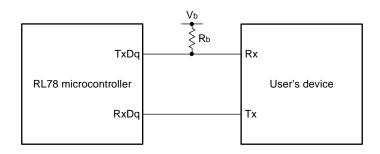
* This value is the theoretical value of the relative difference between the transmission and reception sides.

- Note 6.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

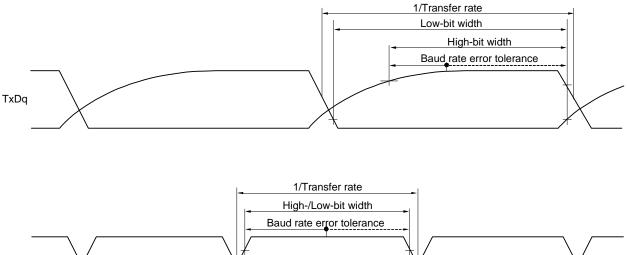
(Remarks are listed on the next page.)



UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



RxDq

Remark 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,

Cb [F]: Communication line (TxDq) load capacitance, Vb [V]: Communication line voltage

Remark 2. q: UART number (q = 0, 1), g: PIM or POM number (g = 1)

Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

TA = -40 to +125°C, 2 Parameter			Conditions	LIC (high an ead	an ala) an a da	Unit
Parameter	Symbol		Conditions	HS (high-speed	,	Unit
				MIN.	MAX.	
SCKp cycle time	tkCY1	$t_{\text{KCY1}} \geq 4/f_{\text{CLK}}$	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V},$	600		ns
			$2.7~V \leq V_b \leq 4.0~V,$			
			C_b = 30 pF, R_b = 1.4 k Ω			
			$2.7~\text{V} \leq \text{V}_\text{DD} < 4.0~\text{V},$	1000		ns
			$2.3~V \leq V_b \leq 2.7~V,$			
			C_b = 30 pF, R_b = 2.7 k Ω			
			$2.4~\text{V} \leq \text{V}_{\text{DD}} < 3.3~\text{V},$	2300		ns
			$1.6~V \leq V_b \leq 2.0~V,$			
			C_b = 30 pF, R_b = 5.5 k Ω			
SCKp high-level width	tĸH1	$4.0~V \leq V_{\text{DD}} \leq$	5.5 V,	tксү1/2 - 150		ns
		$2.7~V \leq V_b \leq 4$.0 V,			
		$C_b = 30 \text{ pF}, \text{ Re}$	o = 1.4 kΩ			
		$2.7 \text{ V} \leq V_{\text{DD}}$ <	4.0 V,	tксү1/2 - 340		ns
		$2.3~V \leq V_b \leq 2$.7 V,			
		$C_b = 30 \text{ pF}, \text{ Re}$	o = 2.7 kΩ			
		$2.4 \text{ V} \leq V_{\text{DD}} <$	3.3 V,	tксү1/2 - 916		ns
		$1.6~V \le V_b \le 2$.0 V,			
		$C_b = 30 \text{ pF}, \text{ Re}$	o = 5.5 kΩ			
SCKp low-level width	t KL1	$4.0~V \leq V_{\text{DD}} \leq$	5.5 V,	tксү1/2 - 24		ns
		$2.7~V \leq V_b \leq 4$.0 V,			
		$C_b = 30 \text{ pF}, \text{ Re}$	o = 1.4 kΩ			
		$2.7 \text{ V} \leq V_{\text{DD}} <$	4.0 V,	tксү1/2 - 36		ns
		$2.3~V \leq V_b \leq 2$.7 V,			
		$C_b = 30 \text{ pF}, \text{ Re}$	o = 2.7 kΩ			
		$2.4 \text{ V} \leq V_{\text{DD}} <$	3.3 V,	tксү1/2 - 1 00		ns
		$1.6~V \le V_b \le 2$.0 V,			
		1		1		

(1/3)

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

 C_b = 30 pF, R_b = 5.5 k Ω

(Remarks are listed two pages after the next page.)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

1	TA40 to +125°C	2 4 V < ΔVח -	- Vnn < 5 5 V	AVss = Vss = 0 V)
	IA = -40 10 + 125 C	, Z.4 V ≤ AVDD =	= v DD ≤ 3.3 v,	AV33 = V33 = UV

(2/3)

Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) ^{Note}	tsıkı		162		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ p\text{F}, \ R_b = 2.7 \ k\Omega \end{array}$	354		ns
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 30 \; p\text{F}, \; R_b = 5.5 \; k\Omega \end{split}$	958		ns
SIp hold time (from SCKp↑) ^{Note}	tksii		38		ns
		$\label{eq:VDD} \begin{split} & 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ & 2.3 \ V \leq V_b \leq 2.7 \ V, \\ & C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	38		ns
		$\label{eq:VDD} \begin{split} & 2.4 \ V \leq V_{DD} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V, \\ & C_b = 30 \ p\text{F}, \ R_b = 5.5 \ k\Omega \end{split}$	38		ns
Delay time from SCKp↓ to SOp output ^{Note}	tkso1			200	ns
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$		390	ns
		$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ p\text{F}, \ R_b = 5.5 \ k\Omega \end{array}$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(T ₁ –	-40 to ±125°C	2 4 V < ΔV - ·	- VDD < 5 5 V	AVss = Vss = 0 V)
(IA =	-40 10 +125 C	, 2.4 v ≤ Av dd :	= V D D ≤ 5.5 V,	AV 55 = V 55 = U V

(3/3)

Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note}	tsıkı		88		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ p\text{F}, \ R_b = 2.7 \ k\Omega \end{array}$	88		ns
		$\label{eq:VDD} \begin{split} & 2.4 \ V \leq V_{DD} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V, \\ & C_b = 30 \ p\text{F}, \ R_b = 5.5 \ k\Omega \end{split}$	220		ns
SIp hold time (from SCKp↓) ^{Note}	tksii		38		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	38		ns
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	38		ns
Delay time from SCKp↑ to SOp output ^{Note}	tkso1			50	ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		50	ns
		$\begin{array}{l} 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$		50	ns

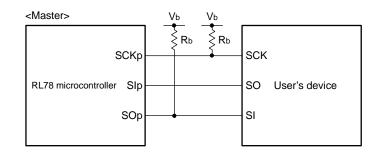
Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)



CSI mode connection diagram (during communication at different potential

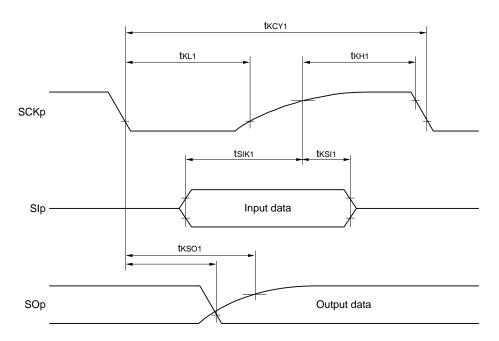


Remark 1. Rb [Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb [F]: Communication line (SCKp, SOp) load capacitance, Vb [V]: Communication line voltage

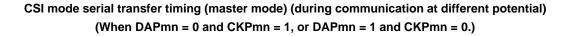
Remark 2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1) **Remark 3.** fMCK: Serial array unit operation clock frequency

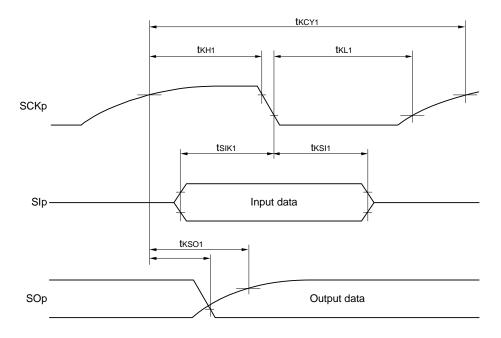
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))





CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Co	onditions	HS (high-spee	ed main) mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 1	tксү2	$4.0~V \leq V_{\text{DD}} \leq 5.5~V,$	$20 \text{ MHz} < f_{\text{MCK}} \leq 24 \text{ MHz}$	24/fмск		ns
		$2.7~V \leq V_b \leq 4.0~V$	$8 \text{ MHz} < f_{\text{MCK}} \leq 20 \text{ MHz}$	20/fмск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \leq 8 \text{ MHz}$	16/fмск		ns
			fмск ≤ 4 MHz	12/fмск		ns
		$2.7~V \leq V_{\text{DD}} < 4.0~V,$	$20 \text{ MHz} < f_{\text{MCK}} \leq 24 \text{ MHz}$	32/f мск		ns
		$2.3~V \leq V_b \leq 2.7~V$	$16 \text{ MHz} < f_{\text{MCK}} \leq 20 \text{ MHz}$	28/fмск		ns
			$8 \text{ MHz} < f_{\text{MCK}} \le 16 \text{ MHz}$	24/fмск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \leq 8 \text{ MHz}$	16/fмск		ns
			fмск ≤ 4 MHz	12/fмск		ns
		$2.4~\textrm{V} \leq \textrm{V}_\textrm{DD} < 3.3~\textrm{V},$	20 MHz $<$ fмск \le 24 MHz	72/fмск		ns
		$1.6~V \leq V_b \leq 2.0~V$	16 MHz $<$ fмск \le 20 MHz	64/fмск		ns
			$8 \text{ MHz} < f_{\text{MCK}} \le 16 \text{ MHz}$	52/fмск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \le 8 \text{ MHz}$	32/f мск		ns
			fмск ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level	t кн2, t кL2	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}, 2$	$2.7~V \leq V_b \leq 4.0~V$	tксү2/2 - 24		ns
width		$2.7~\text{V} \leq \text{V}_{\text{DD}} < 4.0~\text{V}, 2$	$2.3~V \leq V_b \leq 2.7~V$	tксү2/2 - 36		ns
		$2.4~\textrm{V} \leq \textrm{V}_\textrm{DD} < 3.3~\textrm{V},~\textrm{T}$	$1.6~V \leq V_b \leq 2.0~V$	tксү2/2 - 100		ns
SIp setup time	tsik2	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}, 2$	$2.7~V \leq V_b \leq 4.0~V$	1/fмск + 40		ns
(to SCKp↑) ^{Note 2}		$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} < 4.0~\textrm{V}, 2$	$2.3~V \leq V_b \leq 2.7~V$	1/fмск + 40		ns
		$2.4~\textrm{V} \leq \textrm{V}_\textrm{DD} < 3.3~\textrm{V},~\textrm{T}$	$1.6~V \leq V_b \leq 2.0~V$	1/fмск + 60		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi2			1/fмск + 62		ns
Delay time from	tkso2	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}, 2$	$2.7 \text{ V} \le V_b \le 4.0 \text{ V},$		2/fмск + 240	ns
SCKp↓ to SOp output		$C_{\rm b} = 30 \ pF, \ R_{\rm b} = 1.4$	kΩ			
Note 3		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, 2 \\ C_b = 30 \ pF, \ R_b = 2.7 \end{array}$			2/fмск + 428	ns
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, ^{2}$ C _b = 30 pF, Rb = 5.5	$2.4~\text{V} \leq \text{V}_\text{DD} < 3.3~\text{V},~1.6~\text{V} \leq \text{V}_\text{b} \leq 2.0~\text{V},$		2/fмск + 1146	ns

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

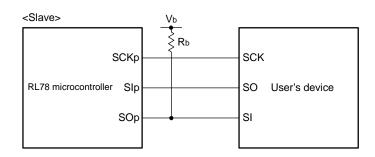
(Notes, Cautions, and Remarks are listed on the next page.)

RL78/I1E



- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp and SCKp pins, and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)

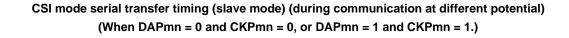


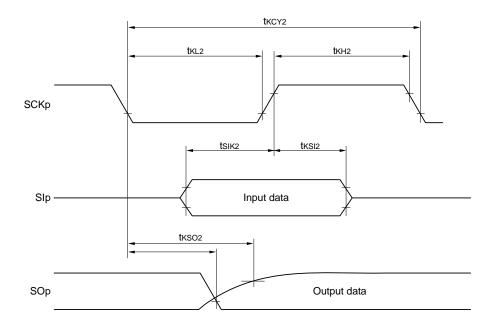
- **Remark 1.** Rb [Ω]: Communication line (SOp) pull-up resistance, Cb [F]: Communication line (SOp) load capacitance, Vb [V]: Communication line voltage
- Remark 2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)
- Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

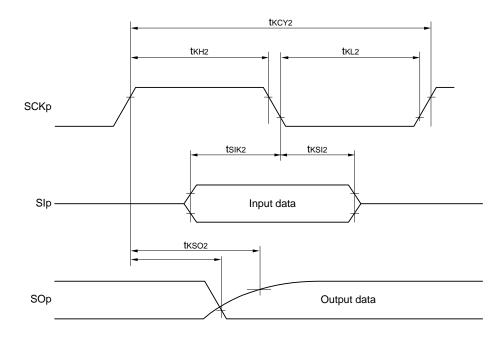
Remark 4. Communication at different potential cannot be performed during clocked serial communication with the slave select function.







CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)
 Remark 2. Communication at different potential cannot be performed during clocked serial communication with the slave select function.

RENESAS

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(1/2)

Parameter	Symbol	Conditions	HS (high-spe	ed main) mode	Unit
			MIN.	MAX.	
SCLr clock frequency	fsc∟			400 Note 1	kHz
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$		400 Note 1	kHz
				100 Note 1	kHz
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 100 \; \text{pF}, \; R_b = 2.7 \; \text{k}\Omega \end{split}$		100 Note 1	kHz
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 100 \; p\text{F}, \; R_b = 5.5 \; k\Omega \end{split}$		100 Note 1	kHz
Hold time when SCLr = "L"	tLow		1200		ns
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	1200		ns
			4600		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; \text{pF}, \; R_b = 2.7 \; \text{k}\Omega \end{array}$	4600		ns
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 100 \; \text{pF}, \; R_b = 5.5 \; \text{k}\Omega \end{split}$	4600		ns
Hold time when SCLr = "H"	tніgн	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	620		ns
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	500		ns
			2700		ns
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 100 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$	2400		ns
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	1830		ns



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(2/2)

Parameter	Symbol	Conditions	HS (high-speed m	HS (high-speed main) mode		
			MIN.	MAX.		
Data setup time (reception)	tsu:dat		1/fмск + 340 Note 1		ns	
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	1/fмск + 340 Note 2		ns	
			1/fмск + 760 Note 2		ns	
		$\label{eq:VD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	1/fмск + 760 Note 2		ns	
		$\label{eq:VD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	1/fмск + 570 Note 2		ns	
Data hold time (transmission)	thd:dat		0	770	ns	
		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	770	ns	
			0	1420	ns	
		$\label{eq:VDD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 100 \; p\text{F}, \; R_b = 2.7 \; k\Omega \end{split}$	0	1420	ns	
		$\label{eq:VDD} \begin{array}{l} 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	0	1215	ns	

Note 1. The value must also be equal to or less than fMCK/4.

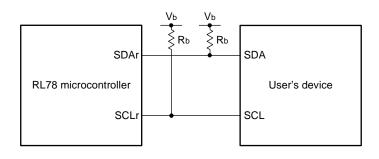
Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the N-ch open drain output (VDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

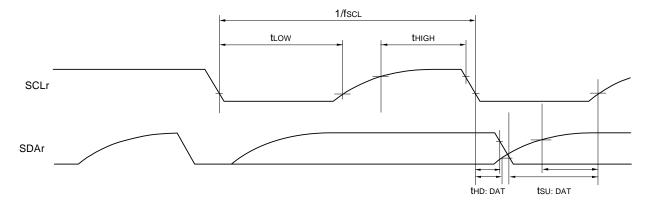
(Remarks are listed on the next page.)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remark 1.** Rb [Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb [F]: Communication line (SDAr, SCLr) load capacitance, Vb [V]: Communication line voltage
- **Remark 2.** r: IIC number (r = 00, 01), g: PIM, POM number (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0), mn = 00, 01)



3.6 Analog Characteristics

3.6.1 Programmable gain instrumentation amplifier and 24-bit ΔΣ A/D converter

(1) Analog input in differential input mode

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dofr = 0 mV, VCOM = 1.0 V, external clock input used)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Full-scale differential input voltage range	Vid	$V_{ID} = (PGAxP - PGAxN) (x = 0 to 3)$		± 800 /Gtotal		mV
Input voltage range	Vı	Each of PGAxP and PGAxN pins (x = 0 to 3)	0.2		1.8	V
Common mode input voltage	Vсом	dofr = 0 mV	0.2+(Vid x Gset1)/2		1.8-(Vid x Gset1)/2	V
Input bias current	lin	VI = 1.0 V			± 50	nA
Input offset current	linofr	VI = 1.0 V			± 20	nA

(2) Analog input in single-ended input mode

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dofr = 0 mV, VCOM = 1.0 V, external clock input used)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage range		Each of PGAxP and PGAxN pins (x = 0 to 3) GSET1 = 1, GSET2 = 1	0.2		1.8	V
Input bias current	lin	VI = 1.0 V			± 50	nA

(3) Programmable gain instrumentation amplifier and 24-bit $\Delta\Sigma$ A/D converter

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dorr = 0 mV, Vcom = 1.0 V, external clock input used, in differential input mode) (1/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES				24	bit
Sampling frequency	fs1	Normal mode		1		MHz
	fS2	Low power mode		0.125		MHz
Output data rate	fdata1	Normal mode	0.48828		15.625	ksps
	fdata2	Low power mode	61.03615		1953.125	sps
Gain setting range	GTOTAL	GTOTAL = GSET1 × GSET2	1		64	V/V
1st gain setting range	GSET1	In differential input mode only		1, 2, 3, 4, 8		V/V
2nd gain setting range	GSET2	In differential input mode only		1, 2, 4, 8		V/V
Offset adjustment bit range	doffb			5		bit
Offset adjustment range	dofr	Referred to input	-164/GSET1		+164/GSET1	mV
Offset adjustment steps	dofs	Referred to input		11/GSET1		mV



(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, normal mode: fs1 = 1 MHz, FDATA	1 = 3.90625
ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dorr = 0 mV, V	сом = 1.0 V,
external clock input used, in differential input mode)	(2/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Gain error	Eg	TA = 25°C GSET1 = 1, GSET2 = 1 Excluding SBIAS error		±0.2	±2.7	%
		TA = 25°C GSET1 = 8, GSET2 = 4 Excluding SBIAS error		±0.1		%
Gain drift ^{Note}	dEG	GSET1 = 1, GSET2 = 1 Excluding SBIAS drift		(5.6)	(22.0)	ppm/°C
		GSET1 = 8, GSET2 = 4 Excluding SBIAS drift		(9.1)		ppm/°C
Offset error	Eos	TA = 25°C GSET1 = 1, GSET2 = 1 Referred to input		±0.32	±2.90	mV
		TA = 25°C GSET1 = 8, GSET2 = 4 Referred to input		±0.03		mV
Offset drift ^{Note}	dEos	GSET1 = 1, GSET2 = 1 Referred to input		(±0.02)	(±6.00)	µV/∘C
		GSET1 = 8, GSET2 = 4 Referred to input		(±0.02)		µV/°C
SND ratio	SNDR	GSET1 = 1, GSET2 = 1, fIN = 50 Hz Normal mode, pin = -1 dBFS	(82)	(85)		dB
		GSET1 = 8, GSET2 = 4, fIN = 50 Hz Normal mode, pin = -1 dBFS	(73)	(80)		dB
Noise	Vn	GSET1 = 1, GSET2 = 1, OSR = 2048		(13)		μVRms
		GSET1 = 8, GSET2 = 4, OSR = 2048		(0.6)		μVRms
Integral non-linearity error	INL	GSET1 = 1, GSET2 = 1, OSR = 2048		(±10)		ppmFS
Common mode rejection ratio	CMRR	VCOM = 1.0 ± 0.8 V, fin = 50 Hz GSET1 = 1, GSET2 = 1 Differential input mode	(72)	(90)		dB
Power supply rejection ratio	PSRR	AVDD = 2.7 to 5.5 V GSET1 = 1, GSET2 = 1 Differential input mode		(85)		dB
ΔΣ A/D converter input clock frequency	fadc		3.8	4	4.2	MHz

 Note
 Calculate the gain drift and offset drift by using the following expression (for 125°C products):

 For gain drift: (MAX(EG(T(-40) to T(125))) - MIN(EG(T(-40) to T(125)))) / (125°C -(-40°C))

 For offset drift: (MAX(Eos(T(-40) to T(125))) - MIN(Eos(T(-40) to T(125)))) / (125°C - (-40°C))

 MAX(EG(T(-40) to T(125))): The maximum value of gain error when the temperature range is -40°C to 125°C

 MIN(EG(T(-40) to T(125))): The maximum value of offset error when the temperature range is -40°C to 125°C

 MAX(Eos(T(-40) to T(125))): The maximum value of offset error when the temperature range is -40°C to 125°C

 MIN(Eos(T(-40) to T(125))): The minimum value of offset error when the temperature range is -40°C to 125°C

 MIN(Eos(T(-40) to T(125))): The minimum value of offset error when the temperature range is -40°C to 125°C

Remark In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.



3.6.2 Sensor power supply (SBIAS)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output voltage range	Vout		0.5		2.2	V
Output voltage setting steps	VSTEP			0.1		V
Output voltage precision	VA	IOUT = 1 mA	(-3)		(+3)	%
Maximum output current	Ιουτ		5			mA
Short circuit current	ISHORT	Vout = 0 V		40	65	mA
Load regulation	Lr	$1 \text{ mA} \le I_{OUT} \le 5 \text{ mA}$			(15)	mV
Power supply rejection ratio	PSRR	AVDD = 5.0 V + 0.1 Vpp ripple f = 100 Hz, lout = 2.5 mA	(45)	(50)		dB

Remark In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

3.6.3 Temperature sensor

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature coefficient for sensor	TCSNS			(756)		µV/°C
Sensor output voltage	VTEMP	TA = 25°C		226.4		mV

Remark In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.



3.6.4 A/D converter characteristics

(1) When positive reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), negative reference voltage (-) = AVss (ADREFM = 0), pins subject to A/D conversion: ANI0 to ANI9 and SBIAS

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = AVDD, negative reference voltage (-) = AVss)

Parameter	Symbol	С	onditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		10	bit
Overall error Note 1	AINL	10-bit resolution	4	$4.0 \text{ V} \leq AV_{\text{DD}} \leq 5.5 \text{ V}$		1.2	±6.5	LSB
		ANI0 to ANI9, SBIAS	2	$2.7 \text{ V} \leq AV_{\text{DD}} \leq 5.5 \text{ V}$		1.2	±7.0	LSB
Conversion time	t CONV	10-bit resolution	4	$4.0 \text{ V} \leq AV_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μS
			2	$2.7 \text{ V} \leq AV_{\text{DD}} \leq 5.5 \text{ V}$	3.1875		39	μS
Zero-scale error Notes 1, 2	Ezs		$4.0 \text{ V} \leq AV_{\text{DD}} \leq 5.5 \text{ V}$			±0.50	%FSR	
			2	$2.7 \text{ V} \leq AV_{\text{DD}} \leq 5.5 \text{ V}$			±0.60	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution ANI0 to ANI9, SBIAS	4	$4.0 \text{ V} \leq AV_{\text{DD}} \leq 5.5 \text{ V}$			±0.50	%FSR
			2	$2.7 \text{ V} \leq AV_{\text{DD}} \leq 5.5 \text{ V}$			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	4	$4.0 \text{ V} \leq AV_{\text{DD}} \leq 5.5 \text{ V}$			±3.5	LSB
		ANI0 to ANI9, SBIAS	2	$2.7 \text{ V} \leq AV_{\text{DD}} \leq 5.5 \text{ V}$			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	2	$2.7 \text{ V} \leq AV_{\text{DD}} \leq 5.5 \text{ V}$			±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI9			AVss		AVdd	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Caution The number of pins depends on the product. For details, see a list of pin functions.

(2) When positive reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), negative reference voltage (-) = AVss (ADREFM = 0), pins subject to A/D conversion: ANI0 to ANI9 and SBIAS

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = VBGR, negative reference voltage (-) = AVss)

Parameter	Symbol	C	Conditions		TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	t CONV	8-bit resolution	$2.7~V \leq AV_{\text{DD}} \leq 5.5~V$	17		39	μS
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	$2.7~V \leq AV_{\text{DD}} \leq 5.5~V$			±0.60	%FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.7~V \leq AV_{\text{DD}} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.7~V \le AV_{\text{DD}} \le 5.5~V$			±1.0	LSB
Internal reference voltage (+)	Vbgr	$2.7 \text{ V} \leq AV_{\text{DD}} \leq 5.5 \text{ V}$		\	/ _{BGR} Note	3	V
Analog input voltage	Vain	ANI0 to ANI9		0		VBGR	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. See the Internal reference voltage characteristics.



3.6.5 12-bit D/A converter

(1) When positive reference voltage (+) = AVDD (DACVRF = 0)

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = AVDD)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	DARES				(12)	bit
Output voltage range	DAOUT	12-bit resolution	0.35		AVDD-0.47	V
Integral non-linearity error	DAILE	12-bit resolution			±4.0	LSB
Differential non-linearity error	DADLE	12-bit resolution			±1.0	LSB
Offset error	DAErr	12-bit resolution			±30	mV
Gain error	DAEG	12-bit resolution			±20	mV
Settling time	DAtset	12-bit resolution, CL = 50 pF, RL = 10 k Ω			(60)	μs

Remark 1. In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment. **Remark 2.** The 12-bit D/A converter characteristics are the values obtained with the configurable amplifier connected.

(2) When positive reference voltage (+) = internal reference voltage (DACVRF = 1)

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = VREFDA)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	DARES				(8)	bit
Internal reference voltage	VREFDA	8-bit resolution	1.34	1.45	1.54	V
Output voltage range	DAOUT	8-bit resolution	0.35		VREFDA	V
Integral non-linearity error	DAILE	8-bit resolution			±1.0	LSB
Differential non-linearity	DADLE	8-bit resolution			±1.0	LSB
error						
Offset error	DAErr	8-bit resolution			±30	mV
Gain error	DAEG	8-bit resolution			±20	mV
Settling time	DAtset	8-bit resolution, CL = 50 pF, RL = 10 k Ω			(60)	μs

Remark 1. In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

Remark 2. The 12-bit D/A converter characteristics are the values obtained with the configurable amplifier connected.

Remark 3. Offset error and gain error do not include error in the internal reference voltage.



3.6.6 Configurable amplifier

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, VCOM = 1/2 AVDD, internally connected voltage follower)

AMP0 configuration SW setting: Positive (+) pin = ANX1, negative (-) pin = ANX0 AMP1 configuration SW setting: Positive (+) pin = ANX3, negative (-) pin = ANX2 AMP2 configuration SW setting: Positive (+) pin = ANX5, negative (-) pin = ANX4

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage	Vin		AVss		AVdd	V
Output voltage	Vol	$I_{L=}$ -1 mA, AV_{DD} = 2.7 to 5.5 V		AVss +0.02	AVss +0.07	V
	Vон	IL= 1 mA, AV _{DD} = 2.7 to 5.5 V	AVDD -0.15	AVdd -0.02		V
Maximum output current	Іоит	$4.5 \text{ V} \leq \text{AV}\text{dd} \leq 5.5 \text{ V}$	±10			mA
		$2.7 \text{ V} \leq \text{AV}\text{dd} \leq 5.5 \text{ V}$	±5			mA
Input-referred offset voltage	Voff	TA = 25°C without trimming IL = 0 mA, VCOM = 1.0 V		±1	±4	mV
		TA = 25°C with trimming IL = 0 mA, VCOM = 1.0 V			±0.35	mV
Temperature coefficient for inputreferred offset voltage	Vотс	IL = 0 mA		(±2)	(±8)	µV/∘C
Slew rate	SR1	Normal mode CL = 50 pF, RL = 10 kΩ		(0.1)		V/µs
	SR2	High-speed mode $C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega$		(0.8)		V/µs
Gain bandwidth	GBW1	Normal mode CL = 50 pF, RL = 10 kΩ		(350)		kHz
	GBW2	High-speed mode $C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega$		(1.8)		MHz
Phase margin	θM1	Normal mode CL = 50 pF, RL = 10 kΩ		(70)		deg
	θ M2	High-speed mode $C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega$		(60)		deg
Settling time	tset1	Normal mode $C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega$		(20)		μs
	tset2	High-speed mode $C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega$		(10)		μs
Peak-to-peak voltage noise	Enb	0.1 to 10 Hz Normal mode CL = 50 pF, RL = 10 k Ω		(2.0)		µVrms
Input-referred noise	En	f = 1 kHz Normal mode CL = 50 pF, RL = 10 k Ω		(70)		nV/√Hz
Common mode rejection ratio	CMRR	f = 1 KHz, CL = 50 pF, RL = 10 k Ω		(70)		dB
Power supply rejection ratio	PSRR	$\begin{array}{l} 2.7 \ V \leq AV_{DD} \leq 5.5 \ V \\ CL = 50 \ pF, \ RL = 10 \ k\Omega \end{array}$		(62)		dB

(Remarks are listed on the next page.)



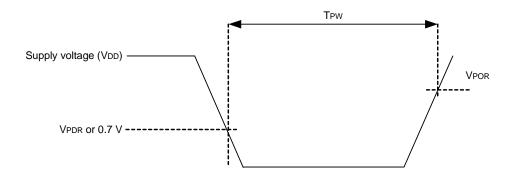
- Remark 1. In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.
- **Remark 2.** The TYP. conditions are the conditions when TA = $25^{\circ}C$ and AVDD = 5.0 V.
- Remark 3. Unless otherwise specified, offset trimming has proceeded.
- Remark 4. Unless otherwise specified, values are for operation in normal mode.

3.6.7 POR characteristics

(TA = -40 to +125°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power on/down reset threshold	VPOR	Voltage threshold on VDD rising	1.48	1.56	1.62	V
	VPDR	Voltage threshold on VDD falling Note 1	1.47	1.55	1.61	V
Minimum pulse width Note 2	TPW		300			μs

- **Note 1.** However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 3.4 AC Characteristics.
- **Note 2.** Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





3.6.8 LVD characteristics

(1) LVD detection voltage in reset mode and interrupt mode

Pa	rameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit			
Voltage detection	Supply voltage level	Vlvd0	Rising edge	4.62	4.74	4.94	V			
threshold			Falling edge	4.52	4.64	4.84	V			
		VLVD1	Rising edge	4.50	4.62	4.82	V			
			Falling edge	4.40	4.52	4.71	V			
		Vlvd2	Rising edge	4.30	4.42	4.61	V			
			Falling edge	4.21	4.32	4.51	V			
		Vlvd3	Rising edge	3.13	3.22	3.39	V			
			Falling edge	3.07	3.15	3.31	V			
		Vlvd4	Rising edge	2.95	3.02	3.17	V			
			Falling edge	2.89	2.96	3.09	V			
		Vlvd5	Rising edge	2.74	2.81	2.95	V			
						Falling edge	2.68	2.75	2.88	V
		Vlvd6	Rising edge	2.55	2.61	2.74	V			
			Falling edge	2.49	2.55	2.67	V			
Minimum pulse wid	İth	t∟w		300			μS			
Detection delay tim	ne					300	μS			

(2) LVD detection voltage in interrupt & reset mode

(TA = -40 to +125°C, VPDR \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Voltage detection	Vlvdd6	Vpoc2,	VPOC1, VPOC0 = 0, 0, 0, falling reset voltage		2.49	2.55	2.67	V
threshold	VLVDD4		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.95	3.02	3.17	V
				Falling interrupt voltage	2.89	2.96	3.09	V
	Vlvdd3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.13	3.22	3.39	V
				Falling interrupt voltage	3.07	3.15	3.31	V
	VLVDD5	VPOC2,	VPOC1, VPOC0 = 0, 0, 1, f	alling reset voltage	2.68	2.75	2.88	V
	VLVDD2		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	4.30	4.42	4.61	V
				Falling interrupt voltage	4.21	4.32	4.51	V
	VLVDD5	VPOC2,	VPOC1, VPOC0 = 0, 1, 0, f	alling reset voltage	2.68	2.75	2.88	V
	VLVDD1		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	4.50	4.62	4.82	V
				Falling interrupt voltage	4.40	4.52	4.71	V
	VLVDD5	VPOC2,	VPOC1, VPOC0 = 0, 1, 1, f	alling reset voltage	2.68	2.75	2.88	V
	Vlvdd3		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	3.13	3.22	3.39	V
				Falling interrupt voltage	3.07	3.15	3.31	V
	VLVDD0		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	4.62	4.74	4.94	V
				Falling interrupt voltage	4.52	4.64	4.84	V

3.6.9 Power supply voltage rising slope characteristics

(TA = -40 to +125°C,	Vss = 0 V)
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Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				50	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 3.4 AC Characteristics.

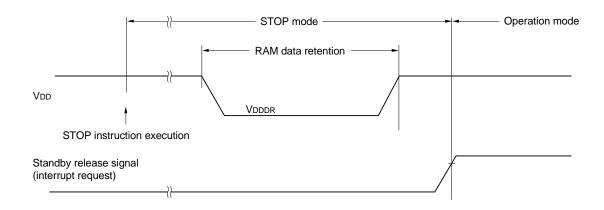
R> 3.7 RAM Data Retention Characteristics

(TA = -40 to +125°C, Vss = 0 V))

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	Vdddr		1.47 Notes 1, 2		5.5	V

Note 1. The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.





3.8 Flash Memory Programming Characteristics

(TA = -40 to +125°C ^{Note 4} , 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	$2.4~V \leq V_{DD} \leq 5.5~V$	1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C ^{Note 5}	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°C ^{Note 5}		1,000,000		
		Retained for 5 years TA = 85°C ^{Note 5}	100,000			
		Retained for 20 years TA = 85°C ^{Note 5}	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

<R>

Note 4. The range is from $T_A = -40$ to $+105^{\circ}C$ when if the flash memory programmer is in use.

Note 5. This temperature is the average value at which data are retained.

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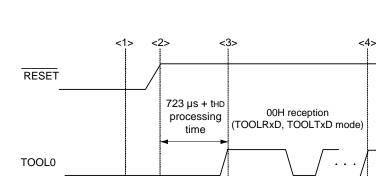
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3.9 Dedicated Flash Memory Programmer Communication (UART)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.10 Timing for Switching Flash Memory Programming Modes

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)						
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuini⊤	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μS
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)		POR and LVD reset must end before the external reset ends.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the external reset ends).

tsu

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit. The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

tSUINIT

- tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
- tHD: How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)



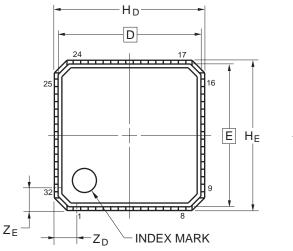
4. PACKAGE DRAWINGS

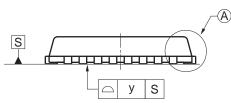
4.1 32-pin products

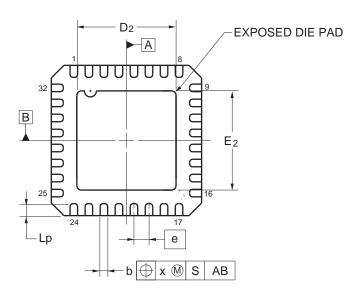
R5F11CBCGNA, R5F11CBCMNA

JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HVQFN32-5x5-0.50	PVQN0032KE-A	P32K9-50B-BAH	0.058

A₁







Dimension in Millimeters Referance Symbol Min Nom Max D 4.75 Ε 4.75 _____ А 0.90 A_1 0.00 b 0.25 0.30 0.20 е 0.50 ____ ____ 0.30 0.40 0.50 Lp 0.10 х ____ _ 0.05 y 4.95 5.00 5.05 H_{D} H_{E} 5.00 5.05 4.95 Z_D 0.75 Z_E 0.75 C₂ 0.19 0.20 0.21 D₂ ____ 3.30 _ E_2 3.30

DETAIL OF A PART

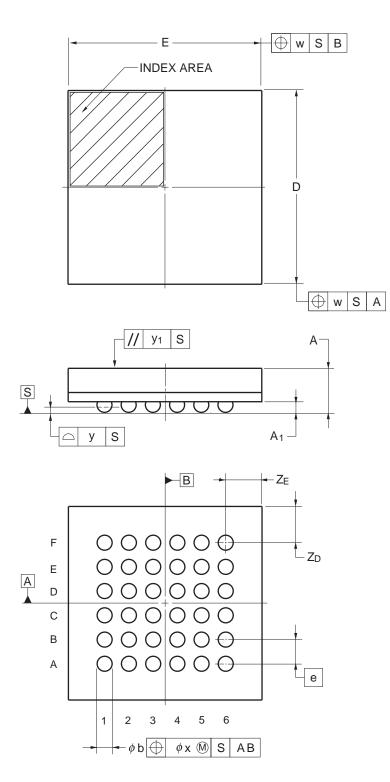


C₂

4.2 36-pin products

R5F11CCCGBG, R5F11CCCMBG

JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-TFBGA36-4x4-0.50	PTBG0036KA-A	P36F1-50-AA6	0.027



Referance	Dimension in Millimeters				
Symbol	Min	Min Nom			
D	3.90	4.00	4.10		
E	3.90	4.00	4.10		
А			1.10		
A1	0.17	0.22	0.27		
е		0.50			
b	0.26	0.31	0.36		
х			0.05		
у			0.08		
У1			0.20		
Z _D		0.75			
ZE		0.75			
w			0.20		

RENESAS

REVISION HISTORY	RL78/I1E Datasheet
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Rev.	Date		Description
Nev. Dale		Page	Summary
1.10	Jun 30, 2016	4	Addition of products name in 1.3.1 32-pin products
		5	Addition of products name in 1.3.2 36-pin products
		10	Change of DTC in 1.6 Outline of Functions
		10	Addition of Note1 in 1.6 Outline of Functions
		43	Change of 2.5.1 (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp external clock in input)
		57	Change of 2.7 RAM Data Retention Characteristics
		57	Change of 2.8 Flash Memory Programming Characteristics
		62	Change of 3.2.2 On-chip oscillator characteristics
		91	Change of 3.5.1 (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp external clock in input)
	105		Change of 3.7 RAM Data Retention Characteristics
		105	Change of 3.8 Flash Memory Programming Characteristics
1.00	Jul 31, 2015	—	First Edition issued

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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